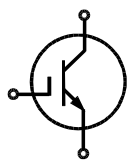
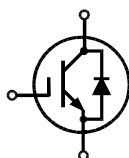


Contents



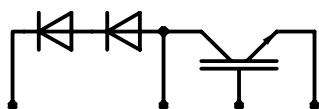
NPT IGBT

V_{CES} max	I_c $T_c = 25^\circ C$	$V_{CE(sat)}$ typ. $T_c = 25^\circ C$	TO-263 (..AS) TO-220	TO-247 ISOPLUS 247™	TO-268	STO-227	Page
V	A	V					
600	32 60	2.2 2.1	IXDP 20N60 B IXDP 35N60 B	IXDH 35N60 B			B5 - 2 B5 - 10
1200	34 38 50 60 100 150	2.8 2.4 2.4 2.4 2.3 2.2	IXDA 20N120 AS	IXDH 20N120 IXDR 30N120 IXDH 30N120	IXDT 30N120	IXDN 55N120 IXDN 75N120	B5 - 16 B5 - 20 B5 - 24 B5 - 28 B5 - 32 B5 - 36



NPT IGBT with Fast Diode

V_{CES} max	I_c $T_c = 25^\circ C$	$V_{CE(sat)}$ typ. $T_c = 25^\circ C$	TO-220	TO-247 ISOPLUS 247™	TO-268	STO-227	Page
V	A	V					
600	32 38 60	2.2 2.2 2.1	IXDP 20N60B D1	IXDR 35N60 BD1 IXDH 35N60 BD1			B5 - 2 B5 - 6 B5 - 10
1200	38 50 60 100	2.4 2.4 2.4 2.3		IXDH 20N120 D1 IXDR 30N120 D1 IXDH 30N120 D1	IXDT 30N120 D1	IXDN 55N120 D1	B5 - 20 B5 - 24 B5 - 28 B5 - 32



NPT IGBT Chopper

V_{CES} max	I_c $T_c = 25^\circ C$	$V_{CE(sat)}$ typ. $T_c = 25^\circ C$	ISOPLUS i4-PAC™	Page
V	A	V		
600	38	1.9	IXFID 35-06C	B5 - 14

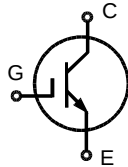
➤ New product

High Voltage IGBT with optional Diode

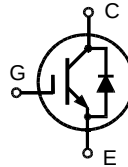
IXDP 20N60 B
IXDP 20N60 BD1

$V_{CES} = 600\text{ V}$
 $I_{C25} = 32\text{ A}$
 $V_{CE(sat) \text{ typ}} = 2.2\text{ V}$

High Speed,
Low Saturation Voltage

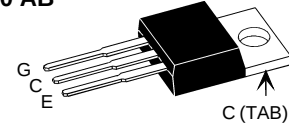


IXDP 20N60B



IXDP 20N60B D1

TO-220 AB



G = Gate,
C = Collector ,

E = Emitter
TAB = Collector

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 20\text{ k}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	32	A
I_{C90}	$T_C = 90^\circ\text{C}$	20	A
I_{CM}	$T_C = 90^\circ\text{C}$, $t_p = 1\text{ ms}$	40	A
RBSOA	$V_{GE} = \pm 15\text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 22\text{ }\Omega$ Clamped inductive load, $L = 30\text{ }\mu\text{H}$	$I_{CM} = 60$ $V_{CEK} < V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = \pm 15\text{ V}$, $V_{CE} = 600\text{ V}$, $T_J = 125^\circ\text{C}$ $R_G = 22\text{ }\Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	IGBT Diode	140 50 W W
T_J		-55 ... +150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque	0.4 - 0.6	Nm
Weight		2	g

Features

- NPT IGBT technology
- low switching losses
- low tail current
- no latch up
- short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- optional ultra fast diode
- International standard package

Advantages

- Space savings
- High power density

Typical Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

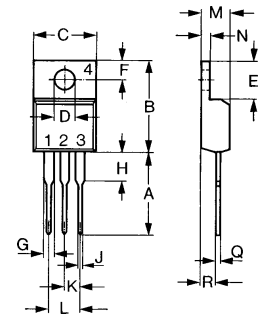
Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 0.4\text{ mA}$, $V_{CE} = V_{GE}$	3		5 V
I_{CES}	$V_{CE} = V_{CES}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		0.7	0.1 mA mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 500\text{ nA}$
$V_{CE(sat)}$	$I_C = 20\text{ A}$, $V_{GE} = 15\text{ V}$		2.2	2.8 V

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		800	pF
C_{oes}			85	pF
C_{res}			50	pF
Q_g	$I_C = 20\text{ A}, V_{GE} = 15\text{ V}, V_{CE} = 480\text{ V}$		70	nC
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 20\text{ A}, V_{GE} = \pm 15\text{ V},$ $V_{CE} = 300\text{ V}, R_G = 22\ \Omega$		25	ns
t_r			30	ns
$t_{d(off)}$			260	ns
t_f			55	ns
E_{on}			0.9	mJ
E_{off}			0.4	mJ
R_{thJC}	Package with heatsink compound	0.5		0.9 K/W
R_{thCH}				K/W

Reverse Diode (FRED) [D1 version only]

Characteristic Values
($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Conditions	min.	typ.	max.
V_F	$I_F = 20\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 20\text{ A}, V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$	2.1 1.6	2.4	V V
I_F	$T_C = 25^\circ\text{C}$ $T_C = 90^\circ\text{C}$		25 15	A A
I_{RM}	$I_F = 10\text{ A}, -di_F/dt = 400\text{ A}/\mu\text{s}, V_R = 300\text{ V}$	11		A
t_{rr}	$V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$	80		ns
t_{rr}	$I_F = 1\text{ A}, -di_F/dt = 100\text{ A}/\mu\text{s}, V_R = 30\text{ V}, V_{GE} = 0\text{ V}$	40		ns
R_{thJC}			2.5	K/W

TO-220 AB Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110

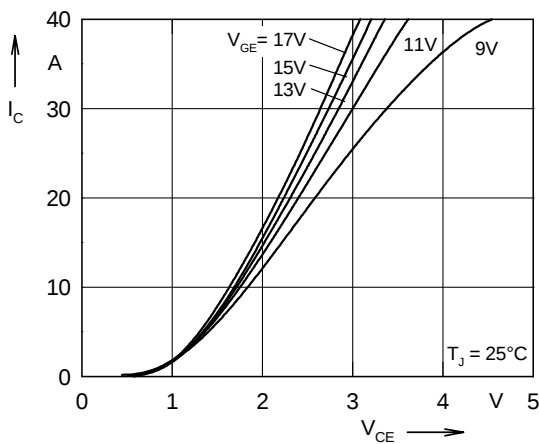


Fig. 1 Typ. output characteristics

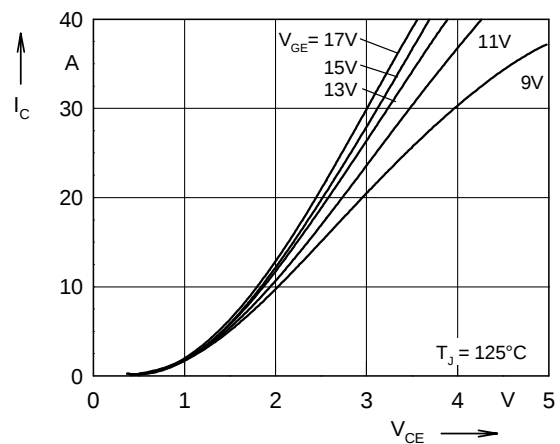


Fig. 2 Typ. output characteristics

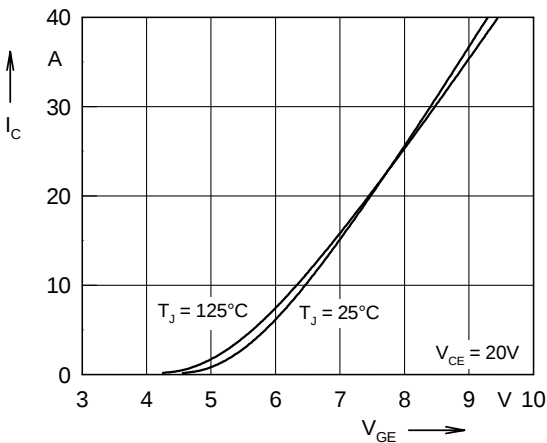


Fig. 3 Typ. transfer characteristics

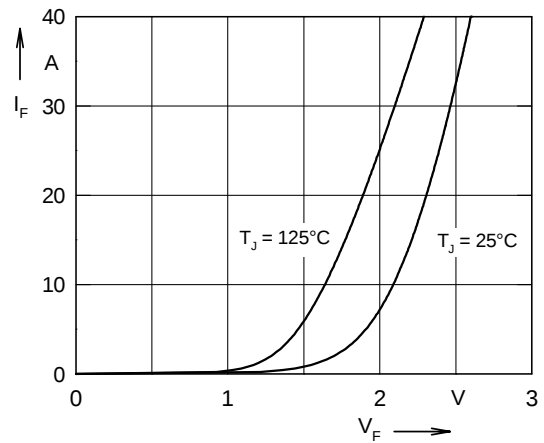


Fig. 4 Typ. forward characteristics of free wheeling diode

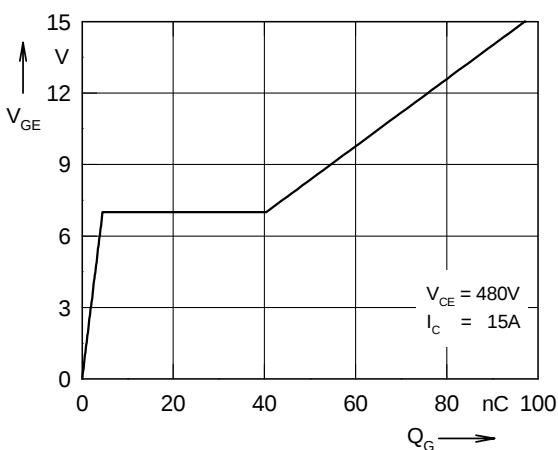


Fig. 5 Typ. turn on gate charge

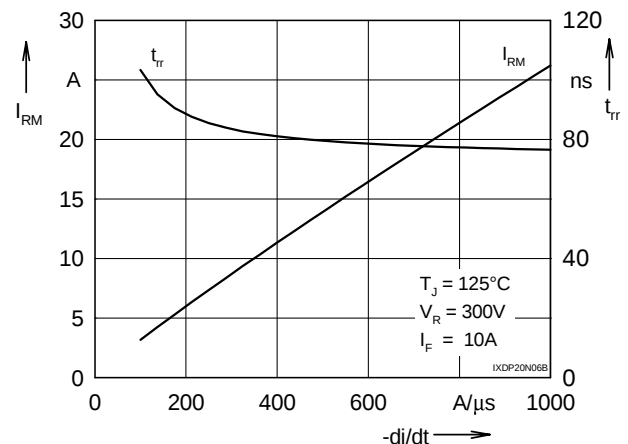


Fig. 6 Typ. turn off characteristics of free wheeling diode

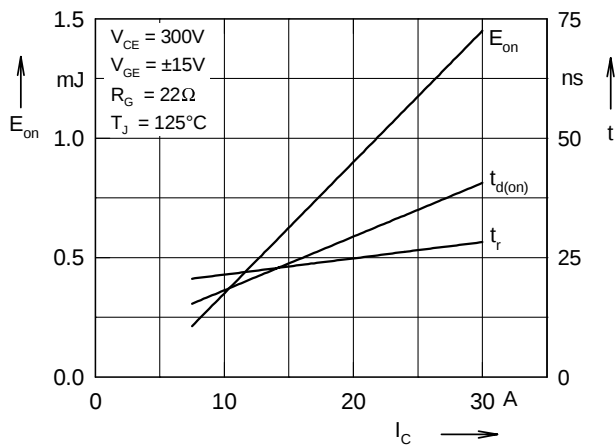


Fig. 7 Typ. turn on energy and switching times versus collector current

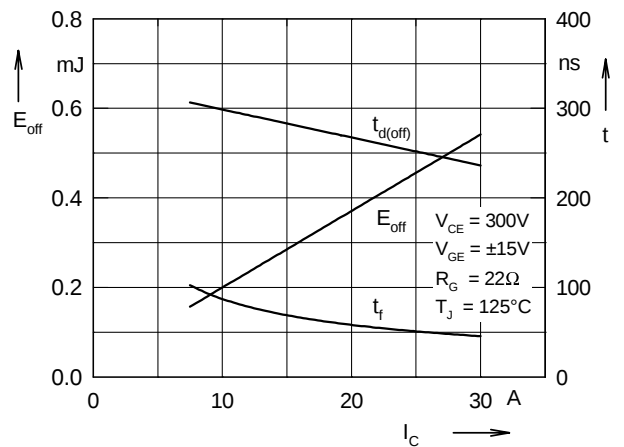


Fig. 8 Typ. turn off energy and switching times versus collector current

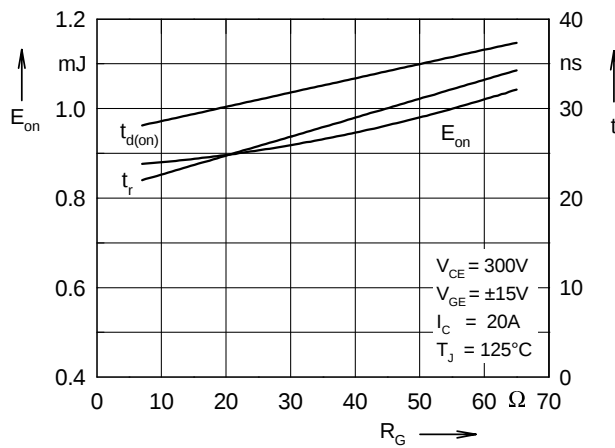


Fig. 9 Typ. turn on energy and switching times versus gate resistor

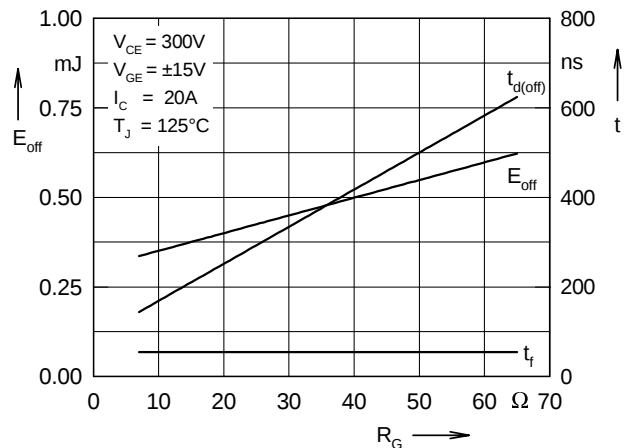


Fig. 10 Typ. turn off energy and switching times versus gate resistor

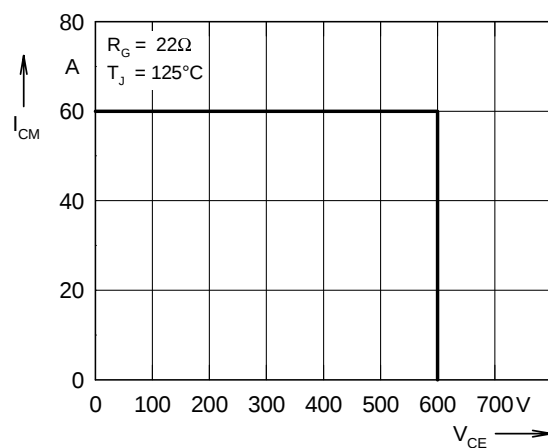


Fig. 11 Reverse biased safe operating area RBSOA

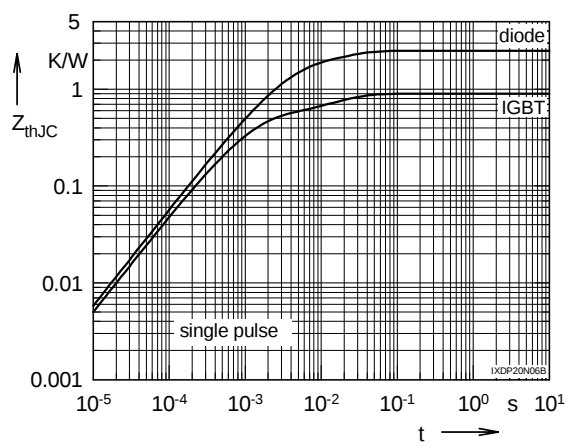


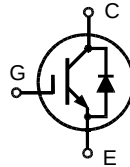
Fig. 12 Typ. transient thermal impedance

IGBT with optional Diode

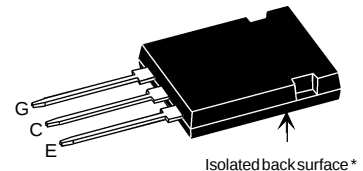
IXDR 35N60 BD1

$$\begin{aligned} V_{CES} &= 600 \text{ V} \\ I_{C25} &= 38 \text{ A} \\ V_{CE(sat) \text{ typ}} &= 2.2 \text{ V} \end{aligned}$$

High Speed,
Low Saturation Voltage



ISOPLUS 247™



G = Gate, E = Emitter
C = Collector, TAB = Collector

* Patent pending

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 20 \text{ k}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	38	A
I_{C90}	$T_C = 90^\circ\text{C}$	24	A
I_{CM}	$T_C = 90^\circ\text{C}, t_p = 1 \text{ ms}$	48	A
RBSOA	$V_{GE} = \pm 15 \text{ V}, T_J = 125^\circ\text{C}, R_G = 10 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 110$ $V_{CEK} < V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = \pm 15 \text{ V}, V_{CE} = 600 \text{ V}, T_J = 125^\circ\text{C}$ $R_G = 10 \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	IGBT Diode	125 50 W W
T_J		-55 ... +150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz RMS; $I_{ISOL} \leq 1 \text{ mA}$	2500	V~
F_C	mounting force with clip	20...120	N
Weight	typical	6	g

Features

- NPT IGBT technology
- low switching losses
- low tail current
- no latch up
- short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- optional ultra fast diode
- Epoxy meets UL 94V-0
- Isolated and UL registered E153432

Advantages

- DCB Isolated mounting tab
- Meets TO-247AD package Outline
- Package for clip or spring mounting
- Space savings
- High power density

Typical Applications

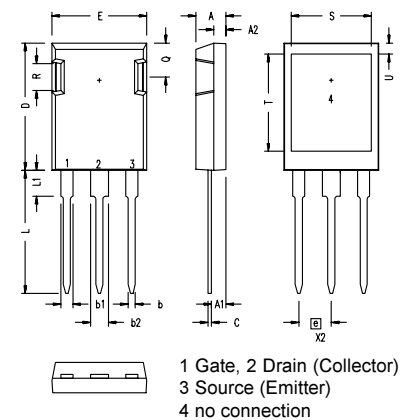
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 0.7 \text{ mA}, V_{CE} = V_{GE}$	3		5 V
I_{CES}	$V_{CE} = V_{CES}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		1	0.1 mA mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 500 \text{ nA}$
$V_{CE(sat)}$	$I_C = 35 \text{ A}, V_{GE} = 15 \text{ V}$		2.2	2.7 V

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		1600	pF
C_{oes}			150	pF
C_{res}			90	pF
Q_g	$I_C = 35\text{ A}, V_{GE} = 15\text{ V}, V_{CE} = 480\text{ V}$		140	nC
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 35\text{ A}, V_{GE} = \pm 15\text{ V},$ $V_{CE} = 300\text{ V}, R_G = 10\ \Omega$		30	ns
t_r			45	ns
$t_{d(off)}$			320	ns
t_f			70	ns
E_{on}			1.6	mJ
E_{off}			0.8	mJ
R_{thJC}	Package with heatsink compound			1 K/W
R_{thCH}			0.25	K/W

Reverse Diode (FRED) [D1 version only]		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Conditions	min.	typ.	max.
V_F	$I_F = 35\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 35\text{ A}, V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$	2.1	2.3	V
I_F	$T_C = 25^\circ\text{C}$ $T_C = 90^\circ\text{C}$		35	A
			18	A
I_{RM}	$I_F = 15\text{ A}, -di_F/dt = 400\text{ A}/\mu\text{s}, V_R = 300\text{ V}$	13		A
t_{rr}	$V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$	90		ns
t_{rr}	$I_F = 1\text{ A}, -di_F/dt = 100\text{ A}/\mu\text{s}, V_R = 30\text{ V}, V_{GE} = 0\text{ V}$	40		ns
R_{thJC}				2.3 K/W

ISOPLUS 247 OUTLINE



Dim.	Millimeter	Inches
	Min.	Max.
A	4.83	5.21
A ₁	2.29	2.54
A ₂	1.91	2.16
b	1.14	1.40
b ₁	1.91	2.13
b ₂	2.92	3.12
C	0.61	0.80
D	20.80	21.34
E	15.75	16.13
e	5.45 BSC	.215 BSC
L	19.81	20.32
L1	3.81	4.32
Q	5.59	6.20
R	4.32	4.83
S	13.21	13.72
T	15.75	16.26
U	1.65	3.03

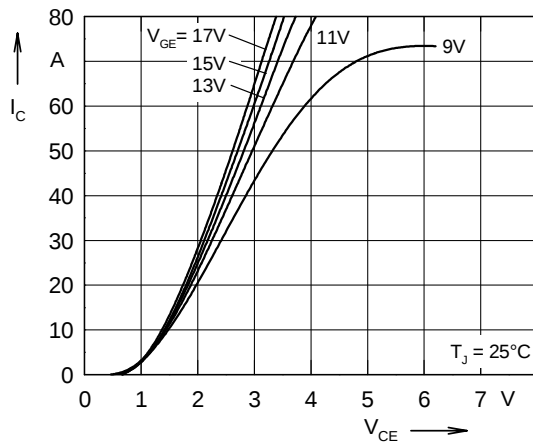


Fig. 1 Typ. output characteristics

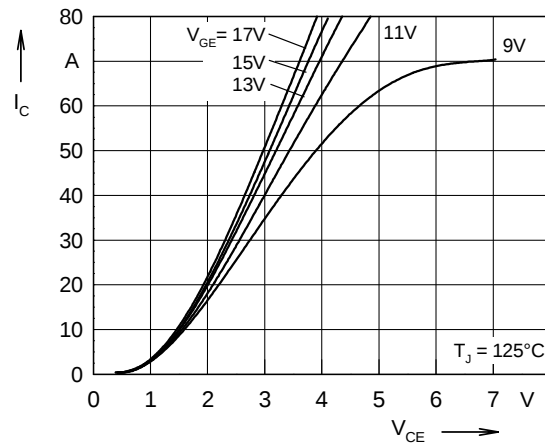


Fig. 2 Typ. output characteristics

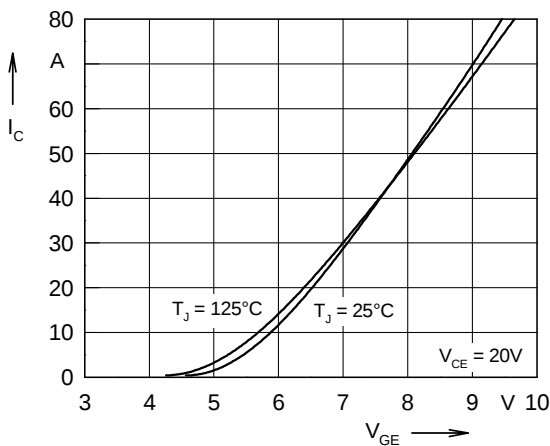


Fig. 3 Typ. transfer characteristics

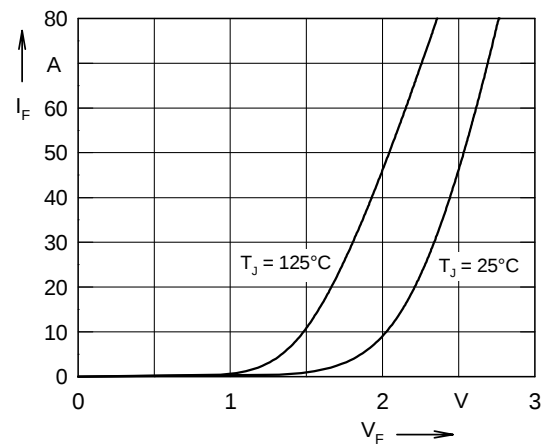


Fig. 4 Typ. forward characteristics of free wheeling diode

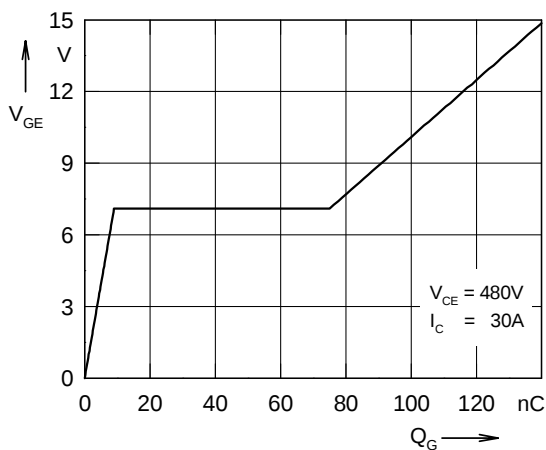


Fig. 5 Typ. turn on gate charge

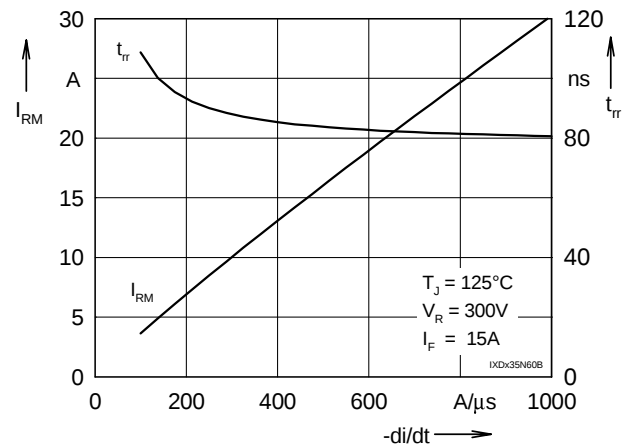


Fig. 6 Typ. turn off characteristics of free wheeling diode

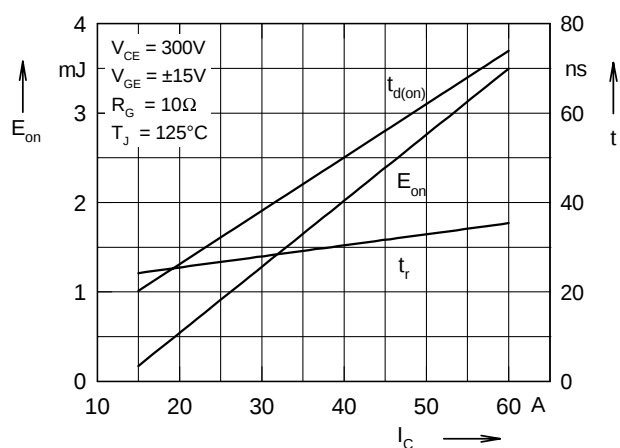


Fig. 7 Typ. turn on energy and switching times versus collector current

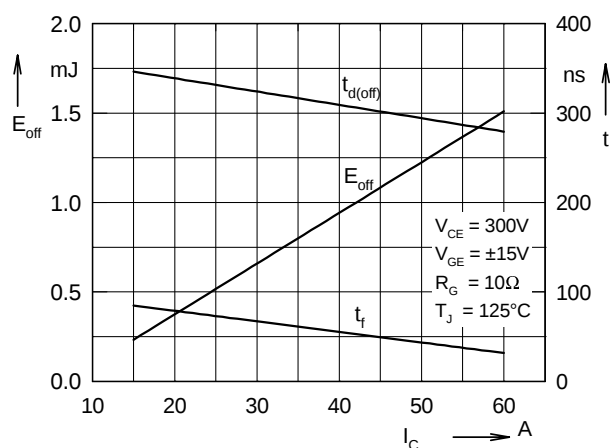


Fig. 8 Typ. turn off energy and switching times versus collector current

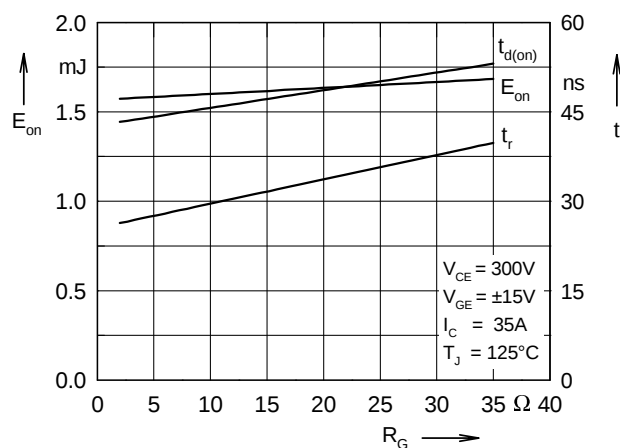


Fig. 9 Typ. turn on energy and switching times versus gate resistor

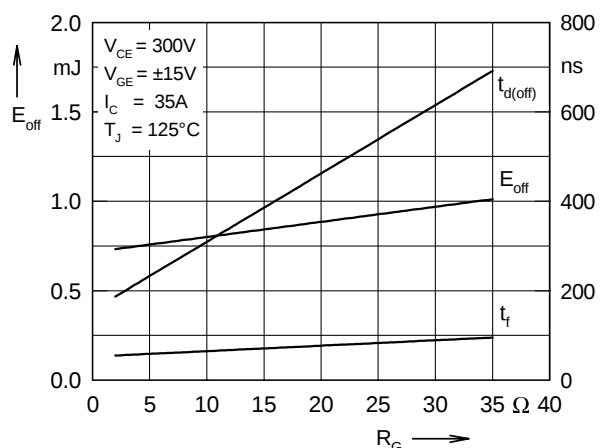


Fig. 10 Typ. turn off energy and switching times versus gate resistor

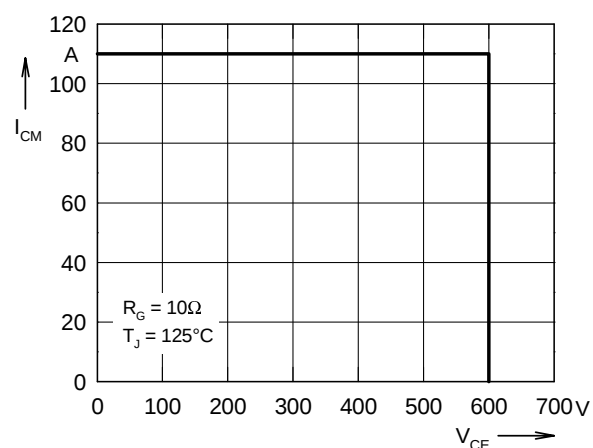


Fig. 11 Reverse biased safe operating area RBSOA

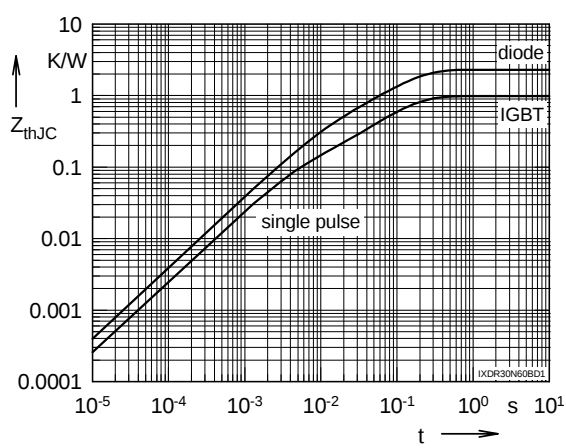


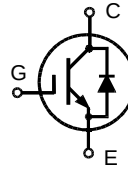
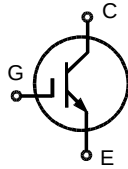
Fig. 12 Typ. transient thermal impedance

IGBT with optional Diode

High Speed,
Low Saturation Voltage

IXDP 35N60 B
IXDH 35N60 B
IXDH 35N60 BD1

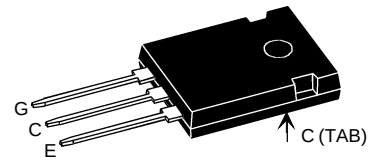
$V_{CES} = 600\text{ V}$
 $I_{C25} = 60\text{ A}$
 $V_{CE(sat) \text{ typ}} = 2.1\text{ V}$



IXDH 35N60 B IXDH 35N60 BD1
IXDP 35N60 B

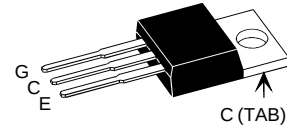
TO-247 AD

IXDH ...



TO-220 AB

IXDP ...



G = Gate, E = Emitter
C = Collector, TAB = Collector

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 20\text{ k}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	60	A
I_{C90}	$T_C = 90^\circ\text{C}$	35	A
I_{CM}	$T_C = 90^\circ\text{C}, t_p = 1\text{ ms}$	70	A
RBSOA	$V_{GE} = \pm 15\text{ V}, T_J = 125^\circ\text{C}, R_G = 10\ \Omega$ Clamped inductive load, $L = 30\ \mu\text{H}$	$I_{CM} = 110$ $V_{CEK} < V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = \pm 15\text{ V}, V_{CE} = 600\text{ V}, T_J = 125^\circ\text{C}$ $R_G = 10\ \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	IGBT Diode	250 80 W W
T_J		-55 ... +150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque	TO-220 TO-247	0.4 - 0.6 0.8 - 1.2 Nm Nm
Weight		6	g

Features

- NPT IGBT technology
- low switching losses
- low tail current
- no latch up
- short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- optional ultra fast diode
- International standard package

Advantages

- Space savings
- High power density

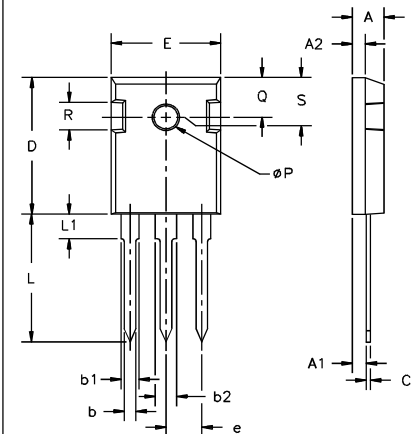
Typical Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

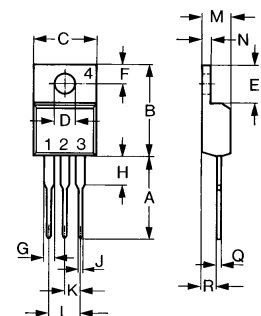
Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 0.7\text{ mA}, V_{CE} = V_{GE}$	3		5 V
I_{CES}	$V_{CE} = V_{CES}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		1	0.1 mA mA
I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$			$\pm 500\text{ nA}$
$V_{CE(sat)}$	$I_C = 35\text{ A}, V_{GE} = 15\text{ V}$		2.2	2.7 V

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		1600	pF
C_{oes}			150	pF
C_{res}			90	pF
Q_g	$I_C = 35\text{ A}, V_{GE} = 15\text{ V}, V_{CE} = 480\text{ V}$		120	nC
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 35\text{ A}, V_{GE} = \pm 15\text{ V},$ $V_{CE} = 300\text{ V}, R_G = 10\ \Omega$		30	ns
t_r			45	ns
$t_{d(off)}$			320	ns
t_f			70	ns
E_{on}			1.6	mJ
E_{off}			0.8	mJ
R_{thJC}				0.5 K/W
R_{thCH}	TO 247 Package with heatsink compound		0.25	K/W
R_{thCH}	TO 220 Package with heatsink compound		0.5	K/W

Reverse Diode (FRED) [D1 version only]		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Conditions	min.	typ.	max.
V_F	$I_F = 35\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 35\text{ A}, V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$		2.1 1.6	2.4 V V
I_F	$T_C = 25^\circ\text{C}$ $T_C = 90^\circ\text{C}$			45 A 25 A
I_{RM}	$I_F = 15\text{ A}, -di_F/dt = 400\text{ A}/\mu\text{s}, V_R = 300\text{ V}$		13	A
t_{rr}	$V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$		90	ns
t_{rr}	$I_F = 1\text{ A}, -di_F/dt = 100\text{ A}/\mu\text{s}, V_R = 30\text{ V}, V_{GE} = 0\text{ V}$		40	ns
R_{thJC}				1.6 K/W

TO-247 AD Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

TO-220 AB Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110

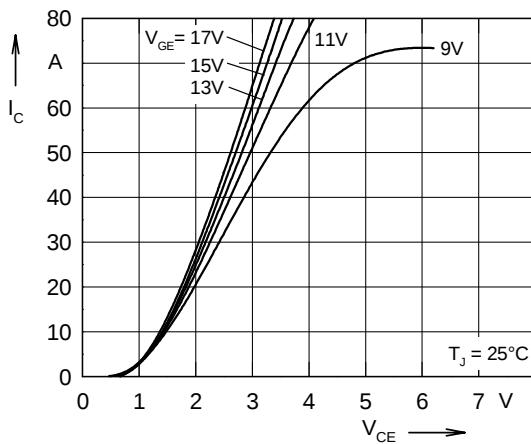


Fig. 1 Typ. output characteristics

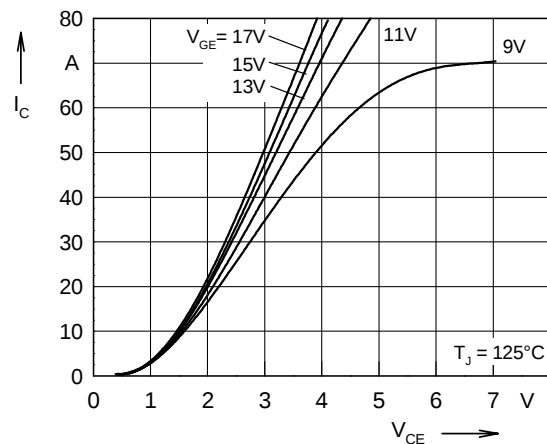


Fig. 2 Typ. output characteristics

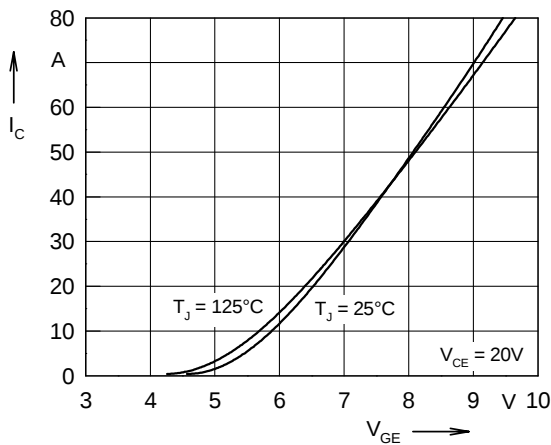


Fig. 3 Typ. transfer characteristics

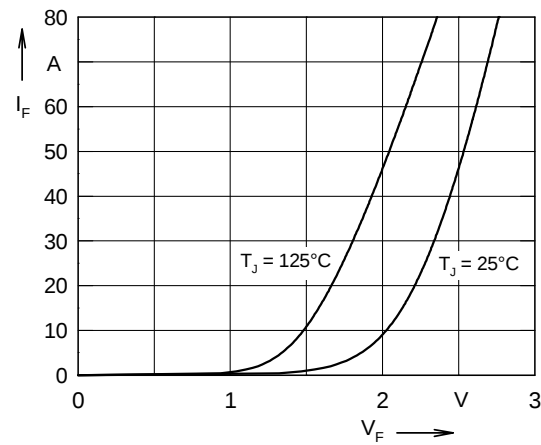


Fig. 4 Typ. forward characteristics of free wheeling diode

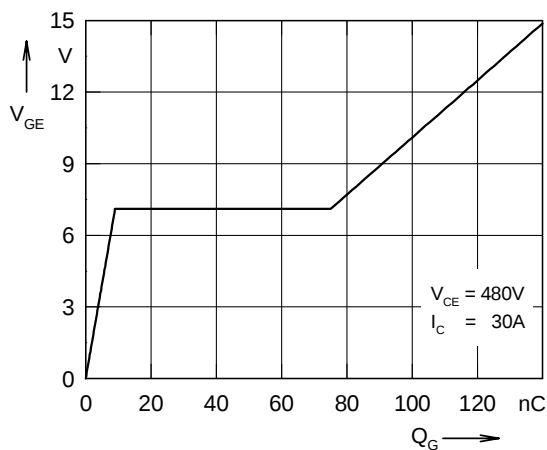


Fig. 5 Typ. turn on gate charge

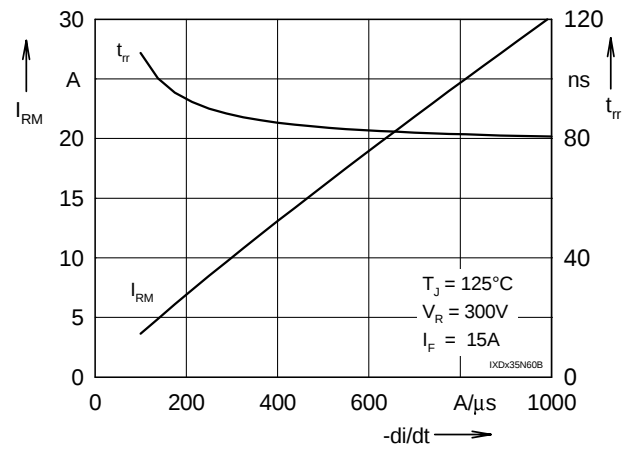


Fig. 6 Typ. turn off characteristics of free wheeling diode

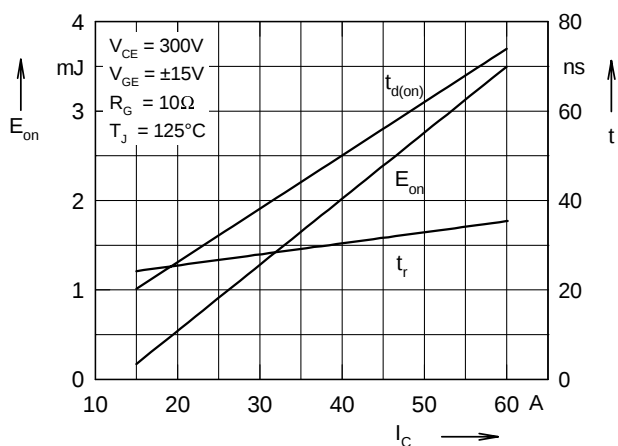


Fig. 7 Typ. turn on energy and switching times versus collector current

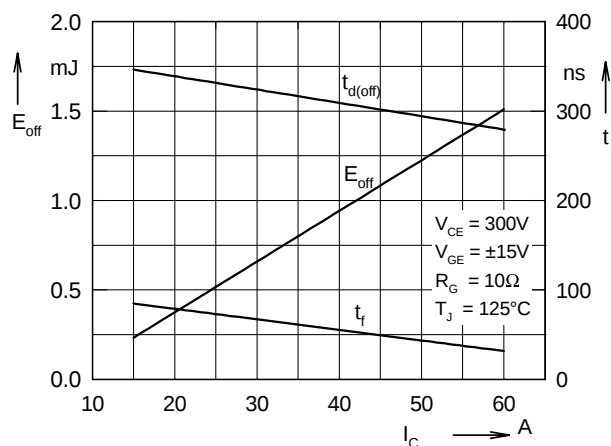


Fig. 8 Typ. turn off energy and switching times versus collector current

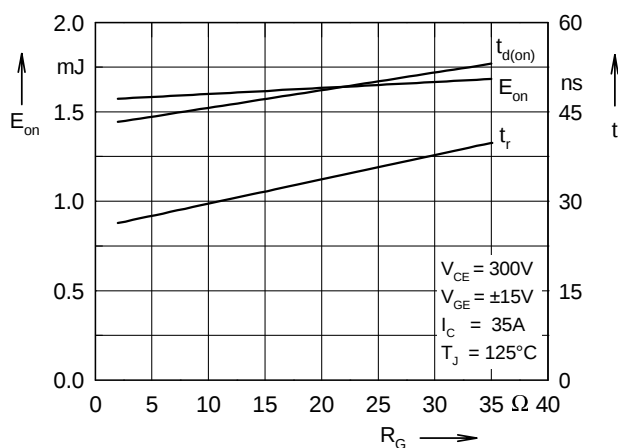


Fig. 9 Typ. turn on energy and switching times versus gate resistor

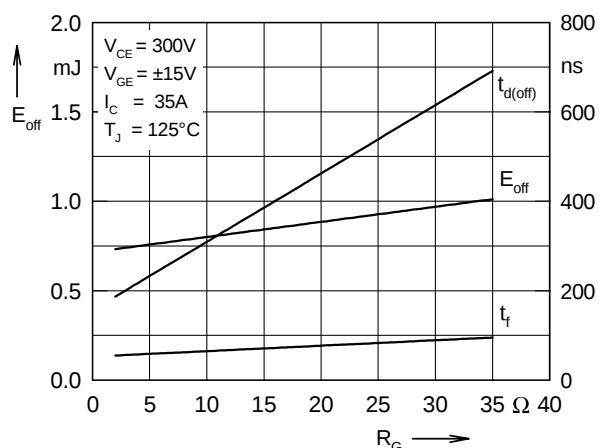


Fig. 10 Typ. turn off energy and switching times versus gate resistor

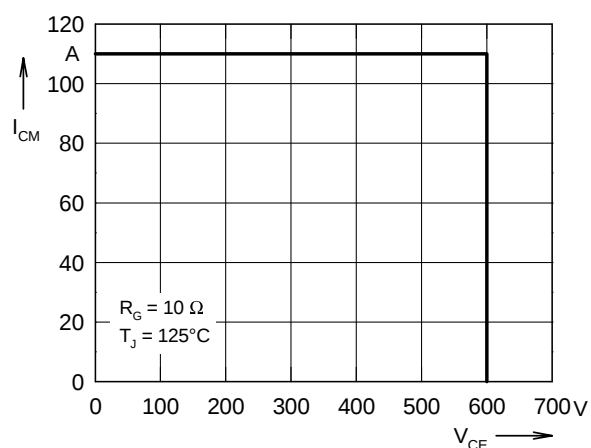


Fig. 11 Reverse biased safe operating area RBSOA

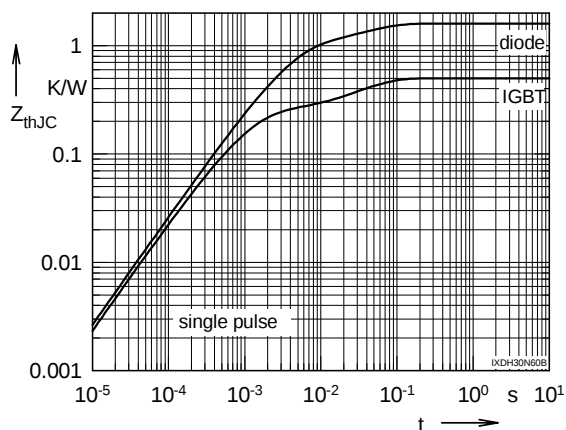
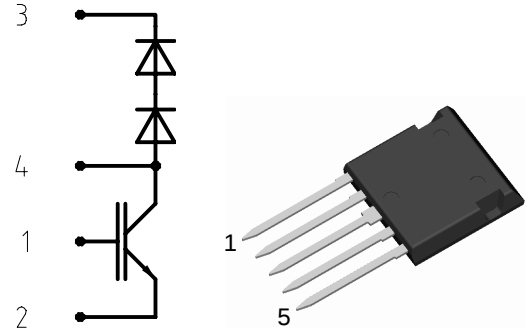


Fig. 12 Typ. transient thermal impedance

Fast IGBT Chopper in ISOPLUS i4-PAC™

FID 35-06C

$I_{C25} = 38 \text{ A}$
 $V_{CES} = 600 \text{ V}$
 $V_{CE(sat) \text{ typ.}} = 1.9 \text{ V}$



IGBT

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	38	A
I_{C90}	$T_C = 90^{\circ}\text{C}$	24	A
I_{CM} V_{CEK}	$V_{GE} = \pm 15 \text{ V}; R_G = 10 \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	110 V_{CES}	A
t_{SC} (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 10 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	125	W

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 25 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.9 2.2		2.4 V
$V_{GE(th)}$	$I_C = 0.7 \text{ mA}; V_{GE} = V_{CE}$	3		5 V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1		0.04 mA mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			200 nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300 \text{ V}; I_C = 25 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 10 \Omega$	30 50 320 70 1.1 0.6		ns ns ns ns mJ mJ
C_{ies} Q_{Gon}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$ $V_{CE} = 600 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 15 \text{ A}$	1600 140		pF nC
R_{thJC}				1.0 K/W

Features

- NPT IGBT technology
 - low switching losses for high frequency operation
 - no latch up
 - positive temperature coefficient for easy paralleling
- HiPerDyn™ FRED
 - consisting of series connected diodes
 - enhanced dynamic behaviour for high frequency operation
- ISOPLUS i4-PAC™ package
 - isolated back surface
 - enlarged creepage towards heatsink
 - application friendly pinout
 - low inductive current path
 - high reliability
 - industry standard outline

Applications

- boost chopper for power factor correction
- supply of high frequency transformer
 - switched mode power supplies
 - welding converters

Diodes (data for series connection)

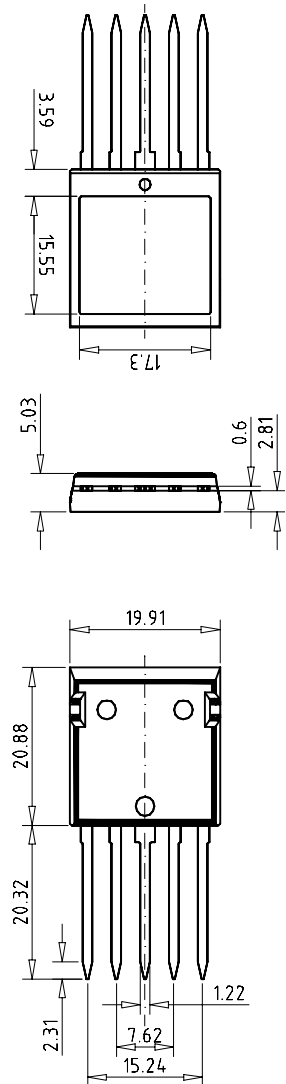
Symbol	Conditions	Maximum Ratings	
V_{RRM}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600	V
I_{F25}	$T_C = 25^{\circ}\text{C}$	35	A
I_{F90}	$T_C = 90^{\circ}\text{C}$	20	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 25\text{ A}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.8	3.7	V
I_R	$V_R = V_{RRM}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.1	0.1	mA
I_{RM} t_{rr}	$I_F = 25\text{ A}; di_F/dt = -400\text{ A}/\mu\text{s}; T_{VJ} = 125^{\circ}\text{C}$ $V_R = 300\text{ V}; V_{GE} = 0\text{ V}$	tbd	tbd	A ns
R_{thJC}	(per diode)		1.2	K/W

Component

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-55...+150	$^{\circ}\text{C}$
T_{stg}		-55...+125	$^{\circ}\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
F_C	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d_S, d_A	pin - pin	1.7		mm
d_S, d_A	pin - backside metal	5.5		mm
R_{thCH}	with heatsink compound	0.15		K/W
Weight		9		g

Dimensions in mm (1 mm = 0.0394")


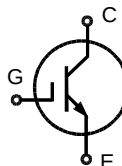
High Voltage IGBT

IXDA 20N120 AS

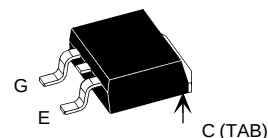
$$\begin{aligned} V_{CES} &= 1200 \text{ V} \\ I_{C25} &= 34 \text{ A} \\ V_{CE(sat) \text{ typ}} &= 2.8 \text{ V} \end{aligned}$$

Short Circuit SOA Capability
Square RBSOA

Preliminary Data



TO-263 AB



E = Emitter, G = Gate, C (TAB) = Collector

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 20 \text{ k}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	34	A
I_{C90}	$T_C = 90^\circ\text{C}$	21	A
I_{CM}	$T_C = 90^\circ\text{C}$, $t_p = 1 \text{ ms}$	42	A
RBSOA	$V_{GE} = \pm 15 \text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 68 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 35$ $V_{CEK} < V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = \pm 15 \text{ V}$, $V_{CE} = V_{CES}$, $T_J = 125^\circ\text{C}$ $R_G = 68 \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$ IGBT	200	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Weight		2	g

Features

- NPT IGBT technology
- high switching speed
- low tail current
- no latch up
- short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- International standard package

Advantages

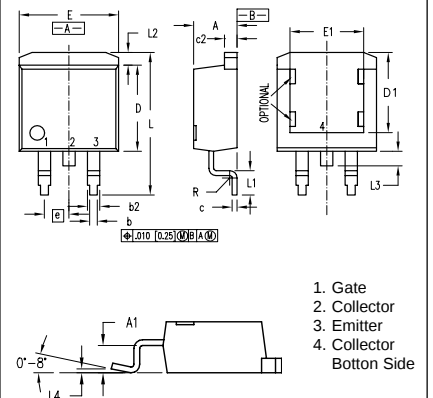
- Space savings
- High power density

Typical Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 0.6 \text{ mA}$, $V_{CE} = V_{GE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		0.8	0.8 mA mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 500 \text{ nA}$
$V_{CE(sat)}$	$I_C = 20 \text{ A}$, $V_{GE} = 15 \text{ V}$		2.8	3.4 V

Symbol	Conditions	Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		1000	pF
C_{oes}			150	pF
C_{res}			70	pF
Q_g	$I_C = 20\text{ A}, V_{GE} = 15\text{ V}, V_{CE} = 0.5\text{ V}_{CES}$		70	nC
$t_{d(on)}$	Inductive load, $T_j = 125^\circ\text{C}$ $I_C = 20\text{ A}, V_{GE} = \pm 15\text{ V},$ $V_{CE} = 600\text{ V}, R_G = 68\ \Omega$		60	ns
t_r			60	ns
$t_{d(off)}$			400	ns
t_f			50	ns
E_{on}			3.5	mJ
E_{off}			2.1	mJ
R_{thJC}				0.63 K/W

TO-263 AB


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	8.00	8.89	.315	.350
E	9.65	10.29	.380	.405
E1	6.22	8.13	.245	.320
e	2.54 BSC		.100 BSC	
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.20	0	.008
R	0.46	0.74	.018	.029

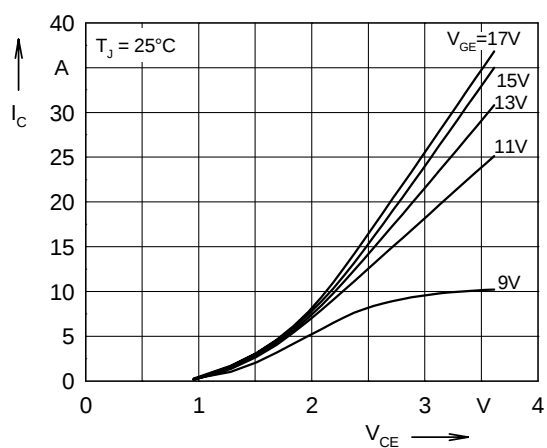


Fig. 1 Typ. output characteristics

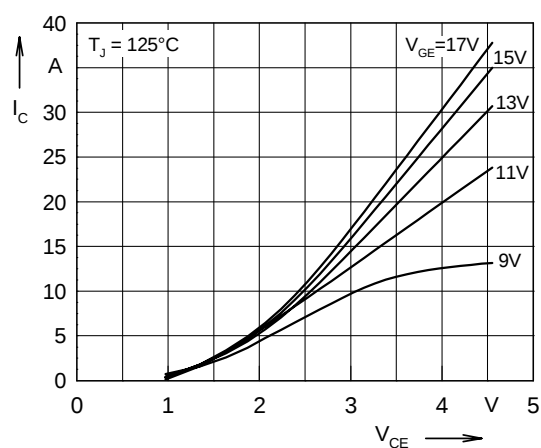


Fig. 2 Typ. output characteristics

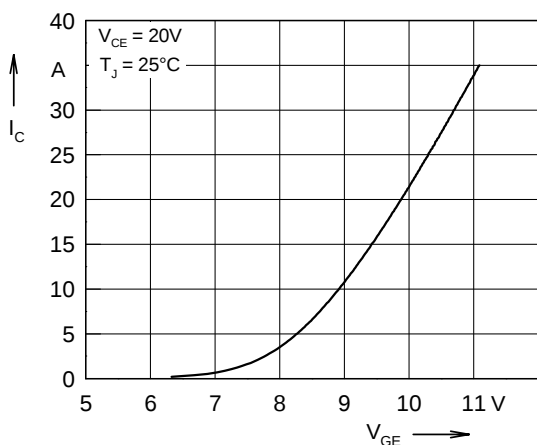


Fig. 3 Typ. transfer characteristics

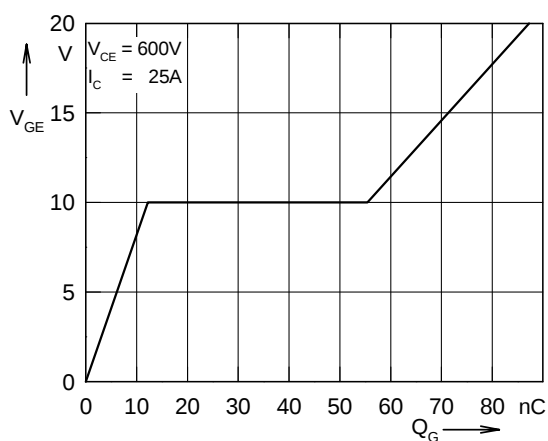


Fig. 4 Typ. turn on gate charge

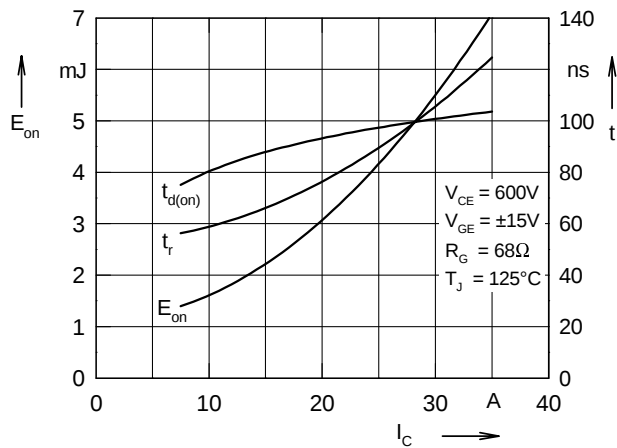


Fig. 5 Typ. turn on energy and switching times versus collector current

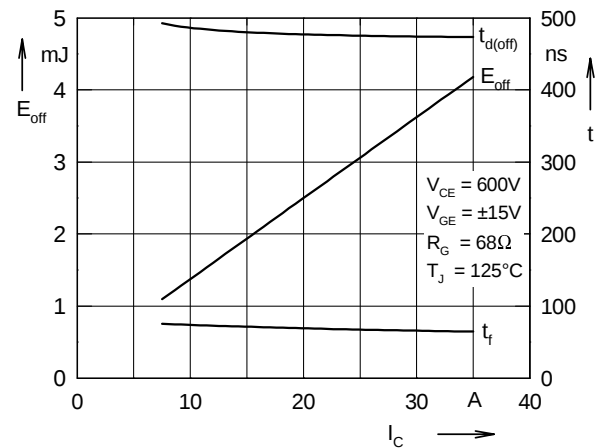


Fig. 6 Typ. turn off energy and switching times versus collector current

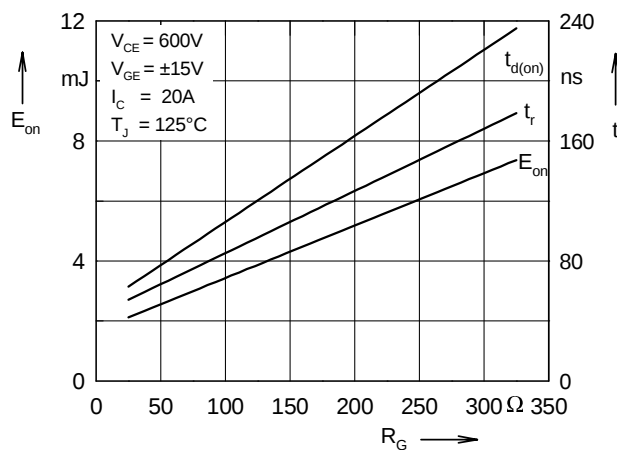


Fig. 7 Typ. turn on energy and switching times versus gate resistor

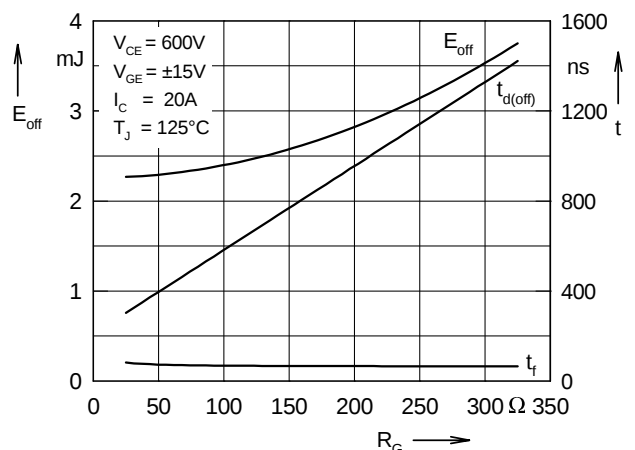


Fig. 8 Typ. turn off energy and switching times versus gate resistor

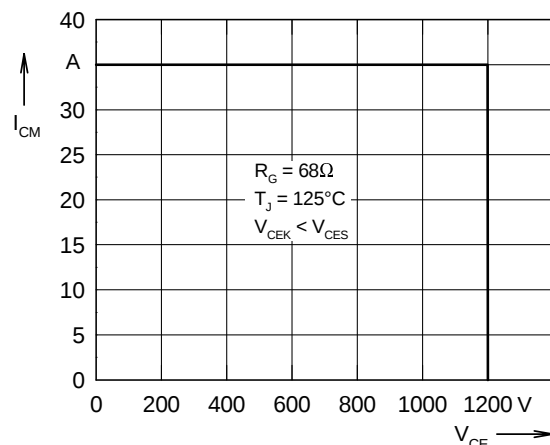


Fig. 9 Reverse biased safe operating area RBSOA

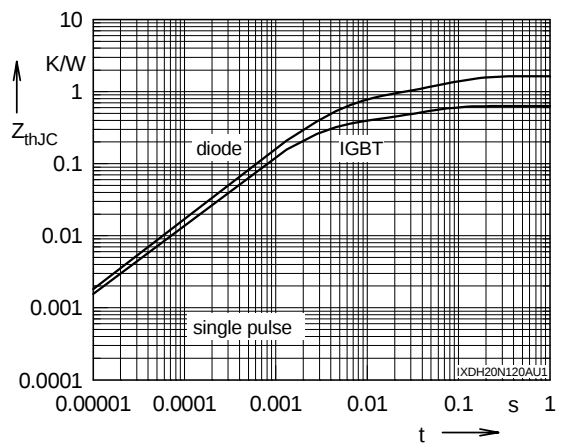


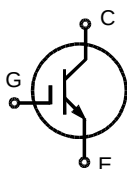
Fig. 10 Typ. transient thermal impedance

High Voltage IGBT with optional Diode

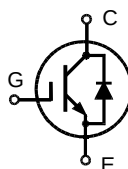
IXDH 20N120
IXDH 20N120 D1

$V_{CES} = 1200\text{ V}$
 $I_{C25} = 38\text{ A}$
 $V_{CE(sat) typ} = 2.4\text{ V}$

Short Circuit SOA Capability
Square RBSOA

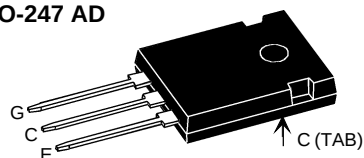


IXDH 20N120



IXDH 20N120 D1

TO-247 AD



G = Gate,
C = Collector ,

E = Emitter
TAB = Collector

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1200	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 20\text{ k}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	38	A
I_{C90}	$T_C = 90^\circ\text{C}$	25	A
I_{CM}	$T_C = 90^\circ\text{C}, t_p = 1\text{ ms}$	50	A
RBSOA	$V_{GE} = \pm 15\text{ V}, T_J = 125^\circ\text{C}, R_G = 82\ \Omega$ Clamped inductive load, $L = 30\ \mu\text{H}$	$I_{CM} = 35$ $V_{CEK} < V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = \pm 15\text{ V}, V_{CE} = V_{CES}, T_J = 125^\circ\text{C}$ $R_G = 82\ \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	IGBT Diode	200 75 W W
T_J		-55 ... +150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque	0.8 - 1.2	Nm
Weight		6	g

Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- optional ultra fast diode
- International standard package

Advantages

- Space savings
- High power density

Typical Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

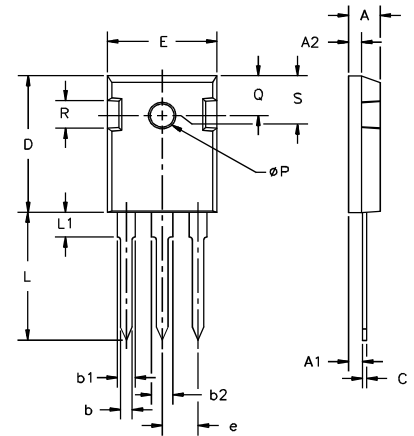
Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 0.6\text{ mA}, V_{CE} = V_{GE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		2	1 mA mA
I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$			$\pm 500\text{ nA}$
$V_{CE(sat)}$	$I_C = 20\text{ A}, V_{GE} = 15\text{ V}$	2.4		3 V

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		1000	pF
C_{oes}			150	pF
C_{res}			70	pF
Q_g	$I_C = 20\text{ A}, V_{GE} = 15\text{ V}, V_{CE} = 0.5\text{ V}_{CES}$		70	nC
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 20\text{ A}, V_{GE} = \pm 15\text{ V},$ $V_{CE} = 600\text{ V}, R_G = 82\ \Omega$		100	ns
t_r			75	ns
$t_{d(off)}$			500	ns
t_f			70	ns
E_{on}			3.1	mJ
E_{off}			2.4	mJ
R_{thJC}	Package with heatsink compound			0.63 K/W
R_{thCH}			0.25	K/W

Reverse Diode (FRED) [D1 version only]

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = 20\text{ A}, V_{GE} = 0\text{ V}$	2.6	2.8	V
	$I_F = 20\text{ A}, V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$	2.1		V
I_F	$T_C = 25^\circ\text{C}$		33	A
	$T_C = 90^\circ\text{C}$		20	A
I_{RM}	$I_F = 20\text{ A}, -di_F/dt = 400\text{ A}/\mu\text{s}, V_R = 600\text{ V}$	15		A
t_{rr}	$V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$	200		ns
t_{rr}	$I_F = 1\text{ A}, -di_F/dt = 100\text{ A}/\mu\text{s}, V_R = 30\text{ V}, V_{GE} = 0\text{ V}$	40		ns
R_{thJC}				1.6 K/W

TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

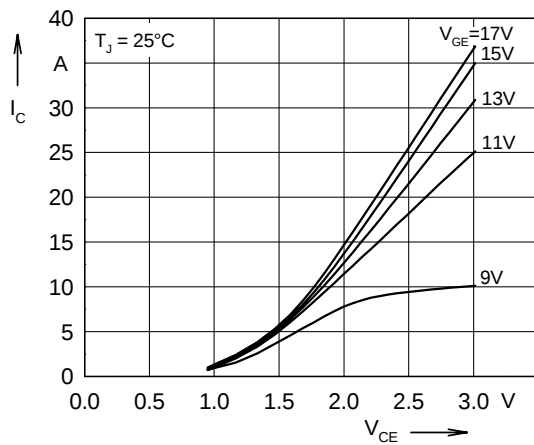


Fig. 1 Typ. output characteristics

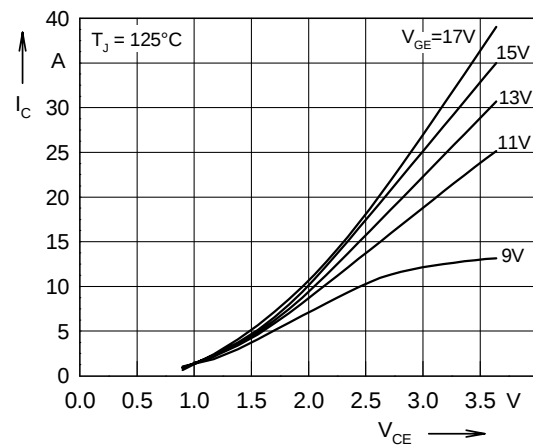


Fig. 2 Typ. output characteristics

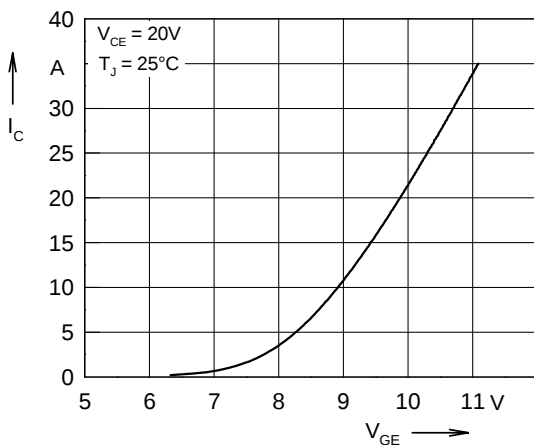


Fig. 3 Typ. transfer characteristics

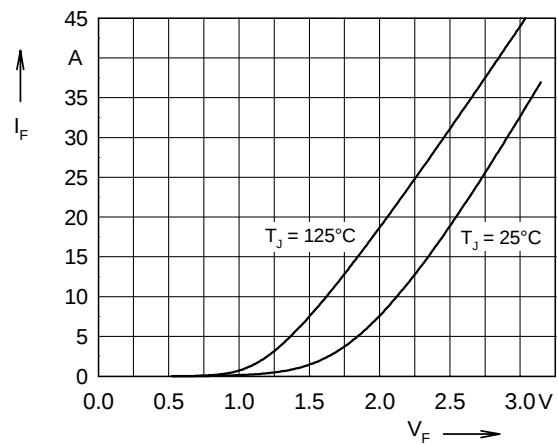


Fig. 4 Typ. forward characteristics of free wheeling diode (D1 version only)

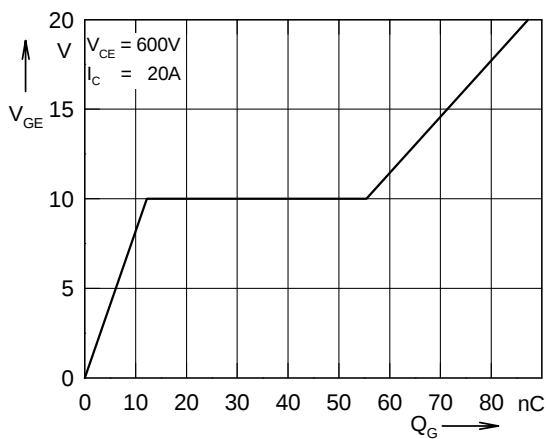


Fig. 5 Typ. turn on gate charge

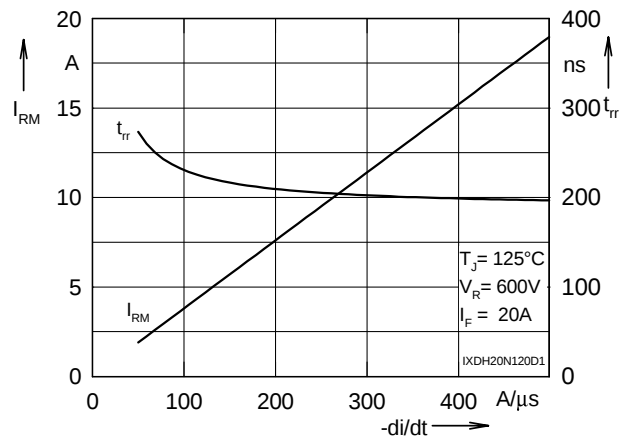


Fig. 6 Typ. turn off characteristics of free wheeling diode (D1 version only)

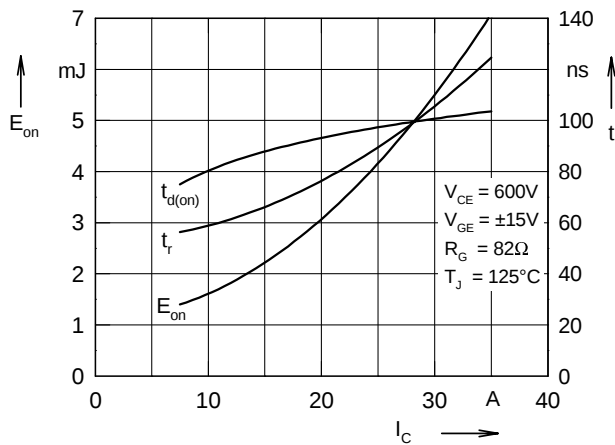


Fig. 7 Typ. turn on energy and switching times versus collector current

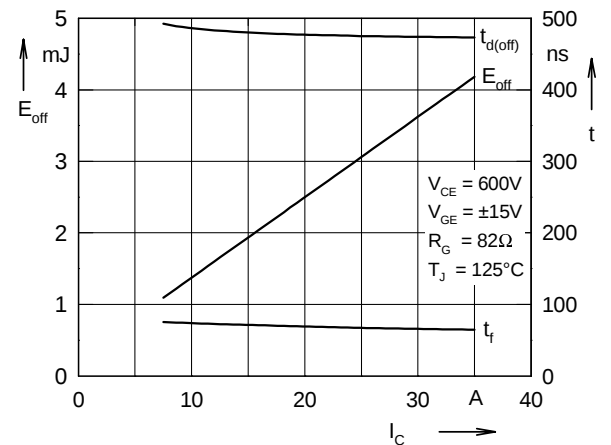


Fig. 8 Typ. turn off energy and switching times versus collector current

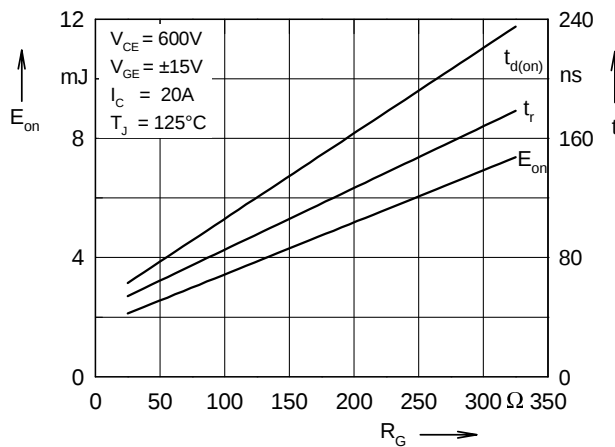


Fig. 9 Typ. turn on energy and switching times versus gate resistor

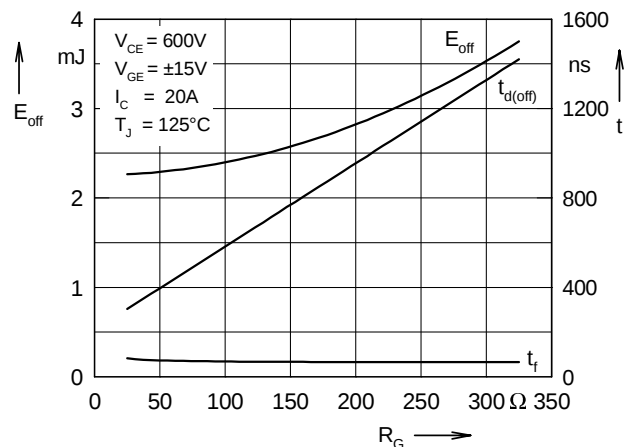


Fig. 10 Typ. turn off energy and switching times versus gate resistor

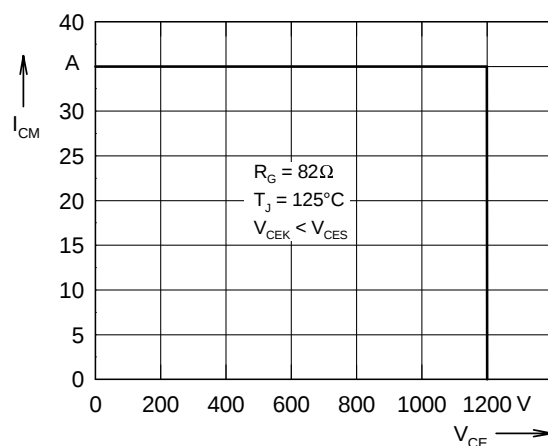


Fig. 11 Reverse biased safe operating area RBSOA

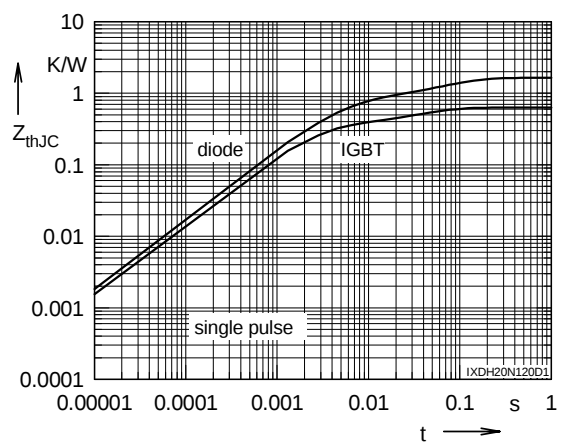


Fig. 12 Typ. transient thermal impedance

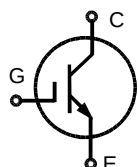
High Voltage IGBT with optional Diode ISOPLUS™ package

(Electrically Isolated Back Side)

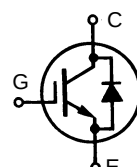
IXDR 30N120 D1
IXDR 30N120

$V_{CES} = 1200\text{ V}$
 $I_{C25} = 50\text{ A}$
 $V_{CE(sat)} \text{ typ} = 2.4\text{ V}$

Short Circuit SOA Capability
Square RBSOA

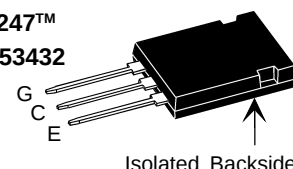


IXDR 30N120



IXDR 30N120 D1

ISOPLUS 247™
E153432



G = Gate C = Collector E = Emitter

*Patent pending

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 20\text{ k}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	50	A
I_{C90}	$T_C = 90^\circ\text{C}$	30	A
I_{CM}	$T_C = 90^\circ\text{C}$, $t_p = 1\text{ ms}$	60	A
RBSOA	$V_{GE} = \pm 15\text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 47\ \Omega$ Clamped inductive load, $L = 30\text{ mH}$	$I_{CM} = 50$ $V_{CEK} < V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = \pm 15\text{ V}$, $V_{CE} = V_{CES}$, $T_J = 125^\circ\text{C}$ $R_G = 47\ \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	IGBT Diode	200 95 W W
T_J		-55 ... +150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1\text{ mA}$	2500	V~
Weight		6	g

Features

- NPT IGBT technology
 - high switching speed
 - low switching losses
 - square RBSOA, no latch up
 - high short circuit capability
 - positive temperature coefficient for easy paralleling
 - MOS input, voltage controlled
 - fast recovery epitaxial diode
- Epoxy meets UL 94V-0
- Isolated and UL registered E153432

Advantages

- DCB Isolated mounting tab
- Meets TO-247AD package Outline
- Package for clip or spring mounting
- Space savings
- High power density

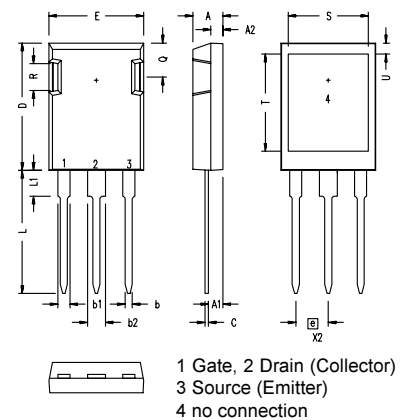
Typical Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 1\text{ mA}$, $V_{CE} = V_{GE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		2.5	1.5 mA mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 500\text{ nA}$
$V_{CE(sat)}$	$I_C = 30\text{ A}$, $V_{GE} = 15\text{ V}$		2.4	2.9 V

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		1650	pF
C_{oes}			250	pF
C_{res}			110	pF
Q_g	$I_C = 30\text{ A}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		120	nC
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 30\text{ A}, V_{GE} = \pm 15\text{ V},$ $V_{CE} = 600\text{ V}, R_G = 47\ \Omega$		100	ns
t_r			70	ns
$t_{d(off)}$			500	ns
t_f			70	ns
E_{on}			4.6	mJ
E_{off}			3.4	mJ
R_{thJC}	Package with heatsink compound			0.6 K/W
R_{thCH}			0.25	K/W

Reverse Diode (FRED)		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Conditions	min.	typ.	max.
V_F	$I_F = 30\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 30\text{ A}, V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$		2.5 2.0	2.7 V V
I_F	$T_C = 25^\circ\text{C}$ $T_C = 90^\circ\text{C}$			50 A 27 A
I_{RM}	$I_F = 30\text{ A}, -di_F/dt = 400\text{ A}/\mu\text{s}, V_R = 600\text{ V}$		20	A
t_{rr}	$V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$		200	ns
t_{rr}	$I_F = 1\text{ A}, -di_F/dt = 100\text{ A}/\mu\text{s}, V_R = 30\text{ V}, V_{GE} = 0\text{ V}$		40	ns
R_{thJC}				1.3 K/W

ISOPLUS 247 OUTLINE


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190
S	13.21	13.72	.520	.540
T	15.75	16.26	.620	.640
U	1.65	3.03	.065	.080

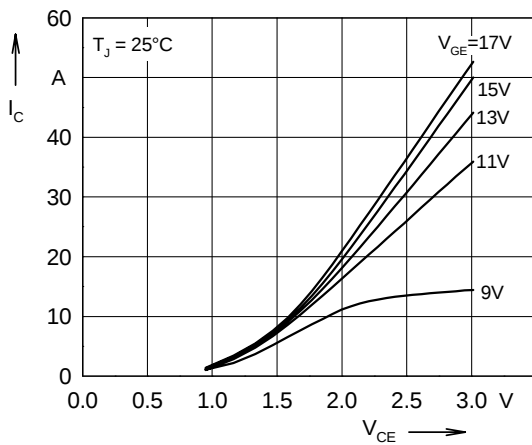


Fig. 1 Typ. output characteristics

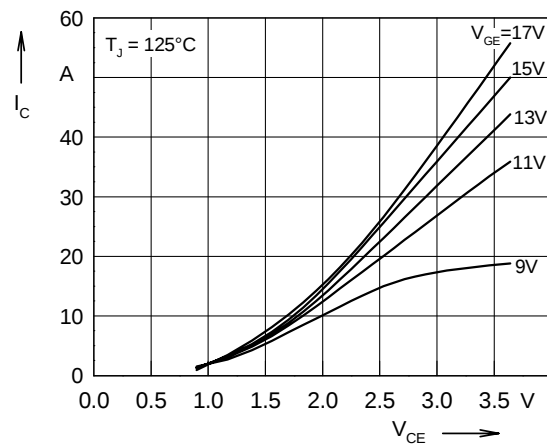


Fig. 2 Typ. output characteristics

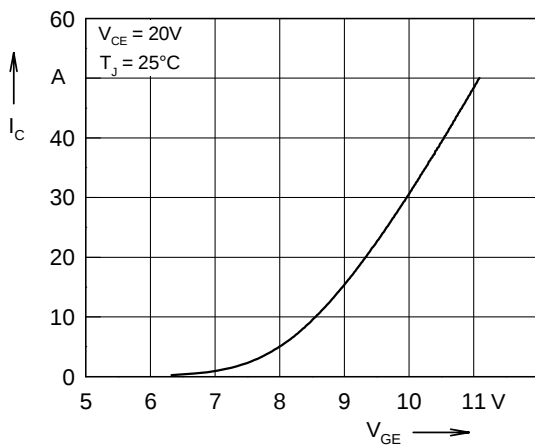


Fig. 3 Typ. transfer characteristics

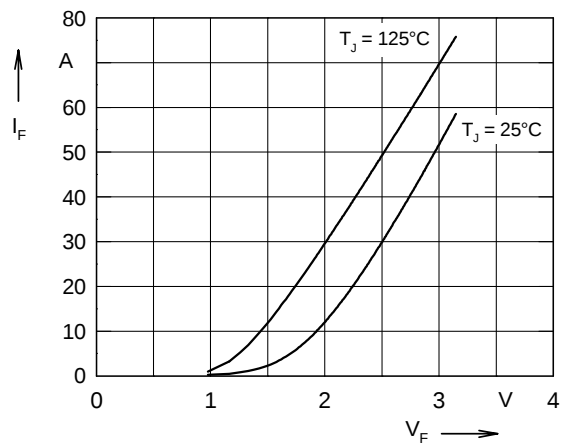


Fig. 4 Typ. forward characteristics of free wheeling diode

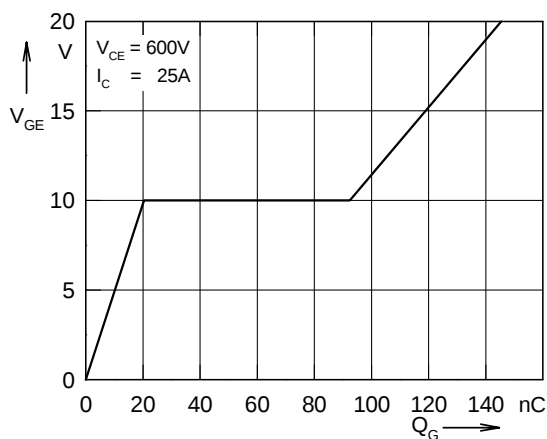


Fig. 5 Typ. turn on gate charge

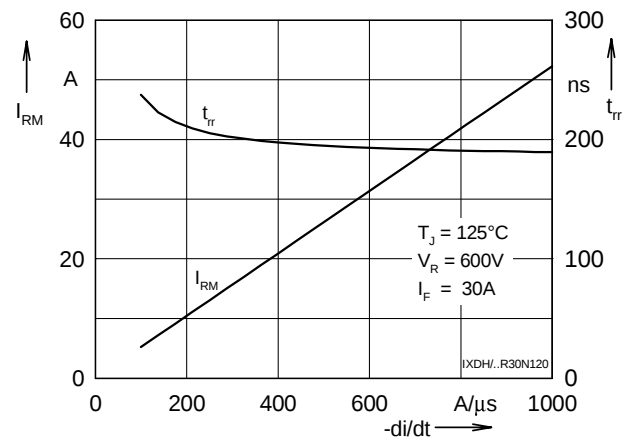


Fig. 6 Typ. turn off characteristics of free wheeling diode

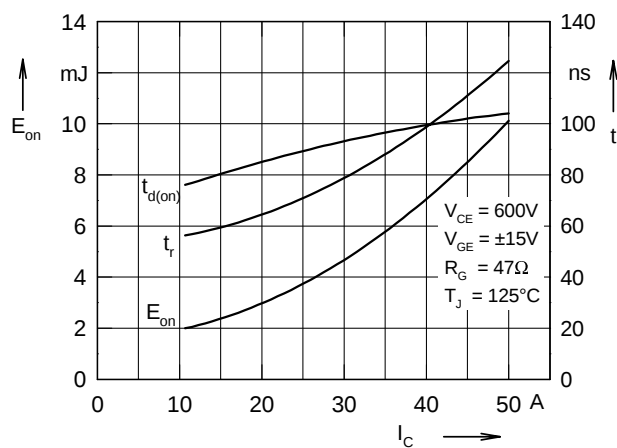


Fig. 7 Typ. turn on energy and switching times versus collector current

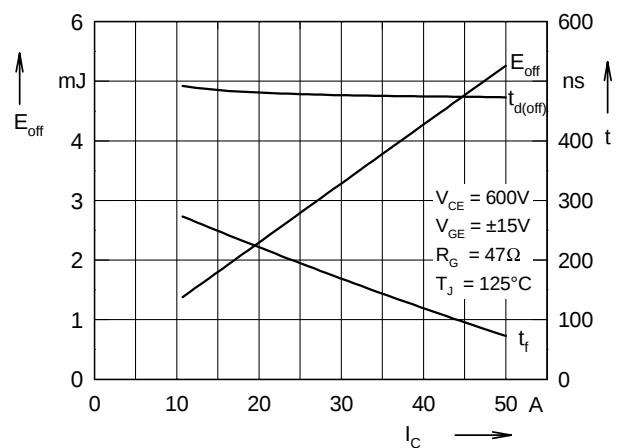


Fig. 8 Typ. turn off energy and switching times versus collector current

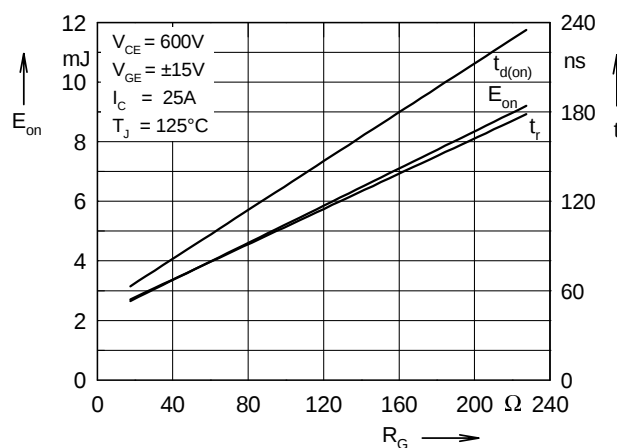


Fig. 9 Typ. turn on energy and switching times versus gate resistor

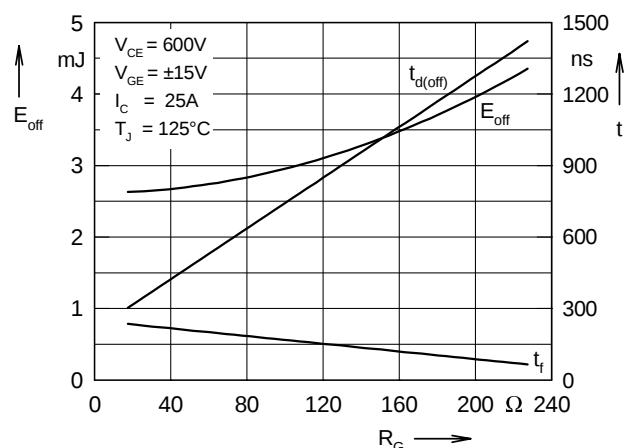


Fig. 10 Typ. turn off energy and switching times versus gate resistor

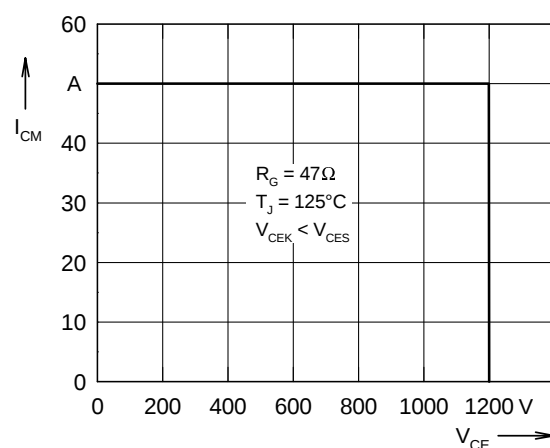


Fig. 11 Reverse biased safe operating area RBSOA

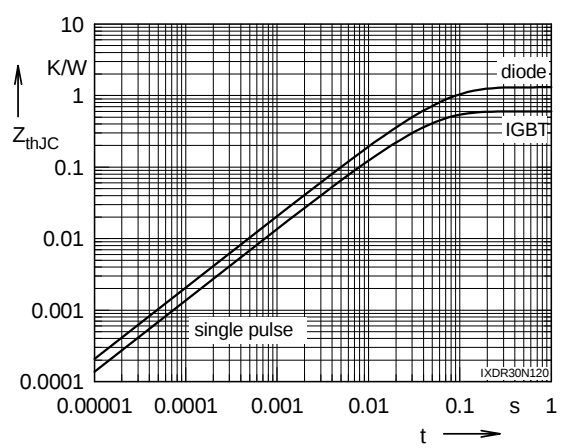


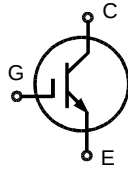
Fig. 12 Typ. transient thermal impedance

High Voltage IGBT with optional Diode

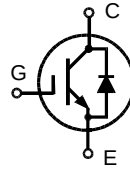
Short Circuit SOA Capability
Square RBSOA

IXDH 30N120
IXDH 30N120 D1
IXDT 30N120
IXDT 30N120 D1

$V_{CES} = 1200 \text{ V}$
 $I_{C25} = 60 \text{ A}$
 $V_{CE(sat) \text{ typ}} = 2.4 \text{ V}$

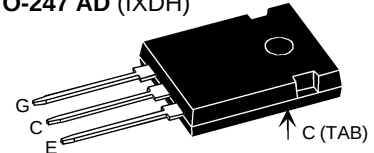


IXDH 30N120
IXDT 30N120

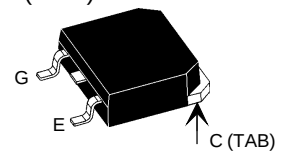


IXDH 30N120 D1
IXDT 30N120 D1

TO-247 AD (IXDH)



TO--268 AA (IXDT)



G = Gate,
C = Collector ,
E = Emitter
TAB = Collector

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 20 \text{ k}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	60	A
I_{C90}	$T_C = 90^\circ\text{C}$	38	A
I_{CM}	$T_C = 90^\circ\text{C}$, $t_p = 1 \text{ ms}$	76	A
RBSOA	$V_{GE} = \pm 15 \text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 47 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 50$ $V_{CEK} < V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = \pm 15 \text{ V}$, $V_{CE} = V_{CES}$, $T_J = 125^\circ\text{C}$ $R_G = 47 \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	IGBT Diode	300 135 W W
T_J		-55 ... +150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque	1.1/10	Nm/lb.in.
Weight		6	g

Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- optional ultra fast diode
- International standard packages

Advantages

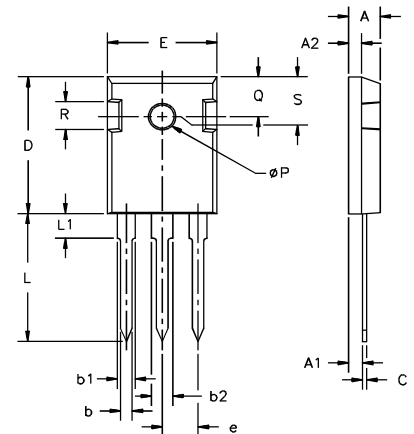
- Space savings
- High power density
- IXDT:
surface mountable high power package

Typical Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 1 \text{ mA}$, $V_{CE} = V_{GE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		2.5	1.5 mA mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 500 \text{ nA}$
$V_{CE(sat)}$	$I_C = 30 \text{ A}$, $V_{GE} = 15 \text{ V}$		2.4	2.9 V

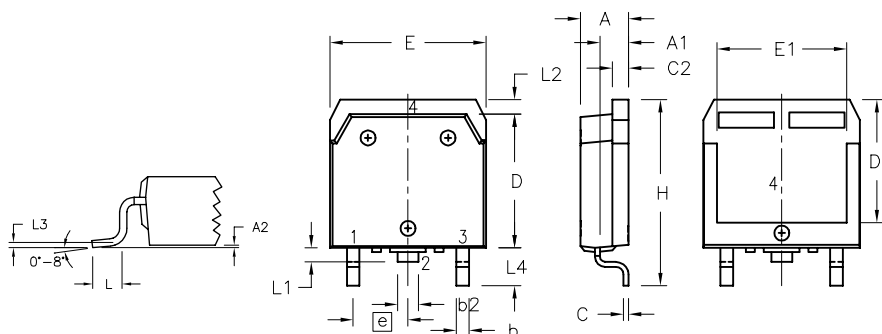
Symbol	Conditions	Characteristic Values		
		(T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
C _{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		1650	pF
C _{oes}			250	pF
C _{res}			110	pF
Q _g	I _C = 30 A, V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		120	nC
t _{d(on)}	Inductive load, T _J = 125°C I _C = 30 A, V _{GE} = ±15 V, V _{CE} = 600 V, R _G = 47 Ω		100	ns
t _r			70	ns
t _{d(off)}			500	ns
t _f			70	ns
E _{on}			4.6	mJ
E _{off}			3.4	mJ
R _{thJC}	Package with heatsink compound			0.42 K/W
R _{thCK}			0.25	K/W

TO-247 AD Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

Reverse Diode (FRED) [D1 version only]
Characteristic Values
(T_J = 25°C, unless otherwise specified)

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V _F	I _F = 30 A, V _{GE} = 0 V	2.5	2.7	V
	I _F = 30 A, V _{GE} = 0 V, T _J = 125°C	2.0		V
I _F	T _C = 25°C		60	A
	T _C = 90°C		35	A
I _{RM}	I _F = 30 A, -di _F /dt = 400 A/μs, V _R = 600 V	20		A
t _{rr}	V _{GE} = 0 V, T _J = 125°C	200		ns
t _{rr}	I _F = 1 A, -di _F /dt = 100 A/μs, V _R = 30 V, V _{GE} = 0 V	40		ns
R _{thJC}				1 K/W

TO-268 AA Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₁	1.9	2.1	.075	.083
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45	BSC	.215	BSC
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3		0.25 BSC		.010 BSC
L4	3.80	4.10	.150	.161

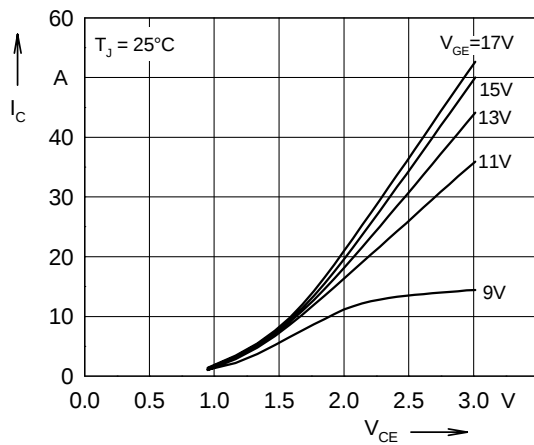


Fig. 1 Typ. output characteristics

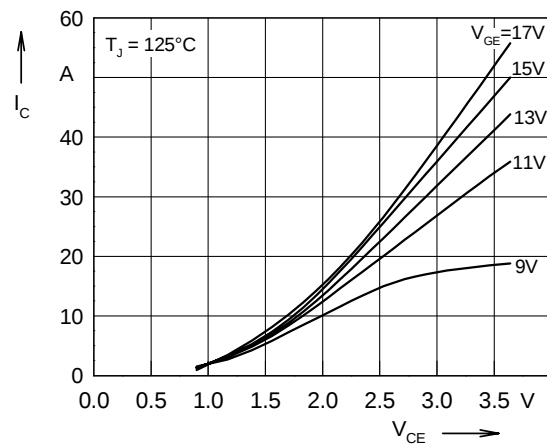


Fig. 2 Typ. output characteristics

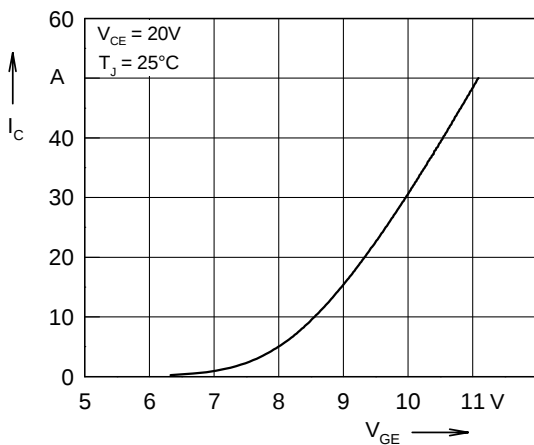


Fig. 3 Typ. transfer characteristics

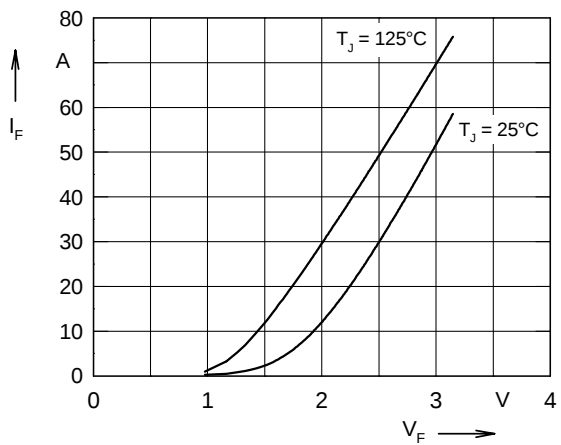


Fig. 4 Typ. forward characteristics of free wheeling diode

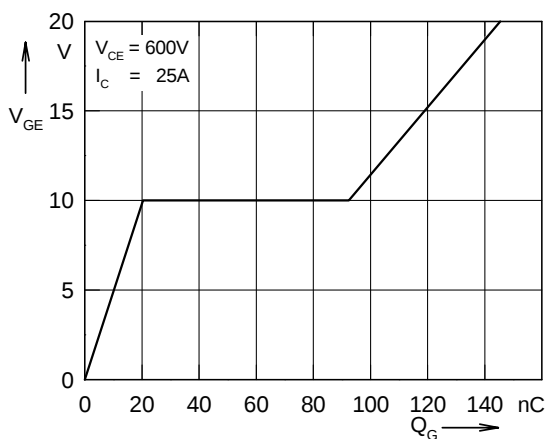


Fig. 5 Typ. turn on gate charge

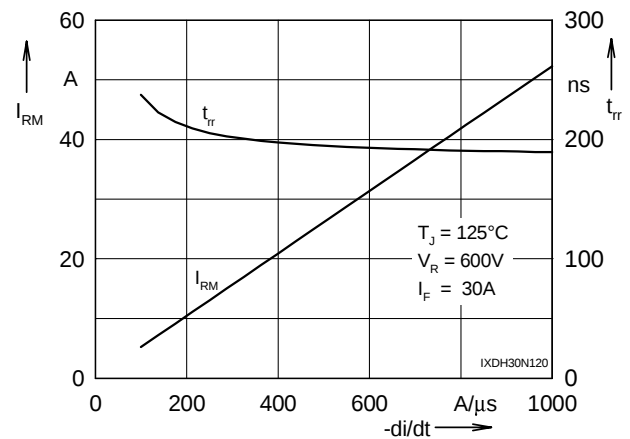


Fig. 6 Typ. turn off characteristics of free wheeling diode

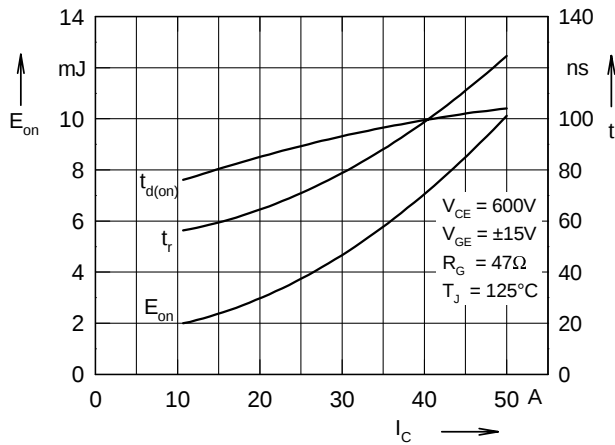


Fig. 7 Typ. turn on energy and switching times versus collector current

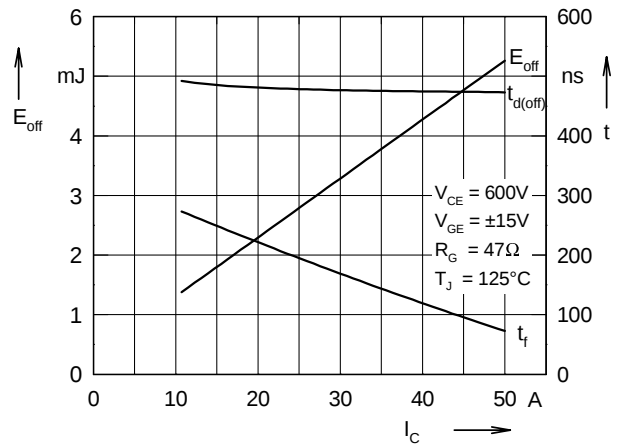


Fig. 8 Typ. turn off energy and switching times versus collector current

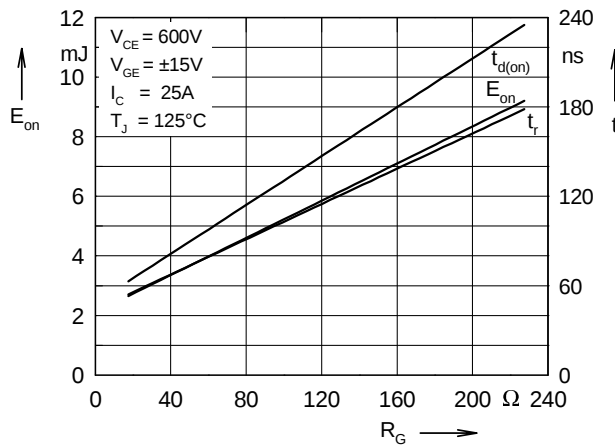


Fig. 9 Typ. turn on energy and switching times versus gate resistor

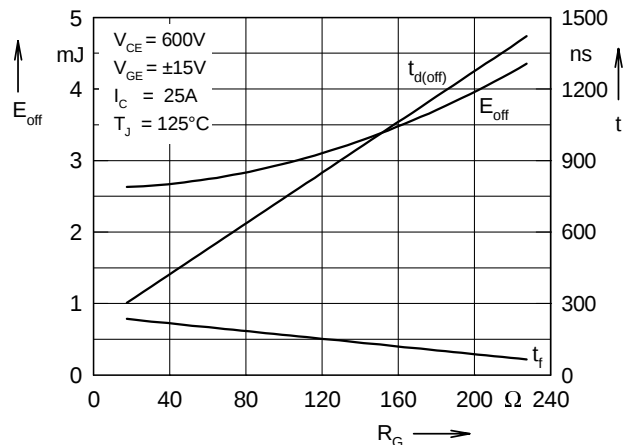


Fig. 10 Typ. turn off energy and switching times versus gate resistor

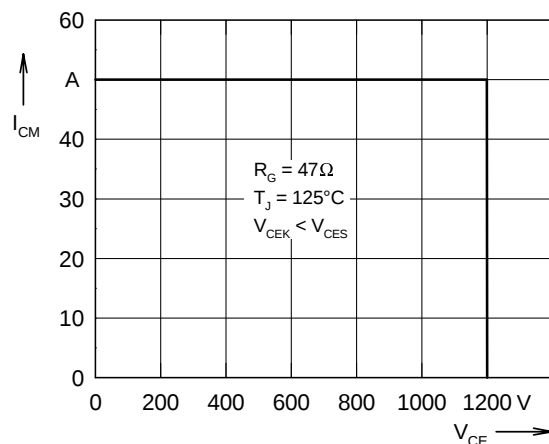


Fig. 11 Reverse biased safe operating area RBSOA

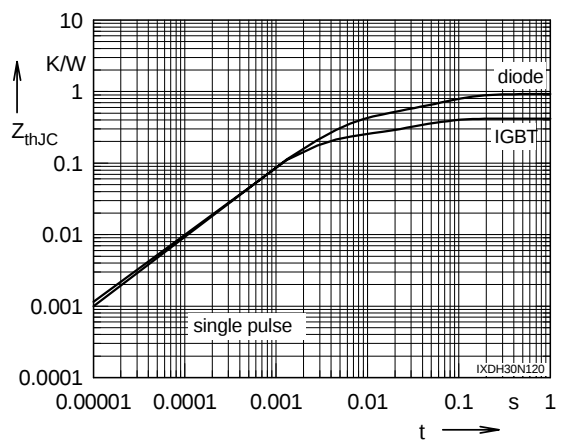


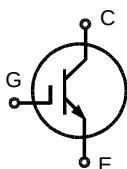
Fig. 12 Typ. transient thermal impedance

High Voltage IGBT with optional Diode

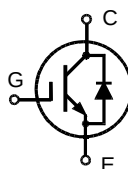
IXDN 55N120
IXDN 55N120 D1

$V_{CES} = 1200 \text{ V}$
 $I_{C25} = 100 \text{ A}$
 $V_{CE(sat) \text{ typ}} = 2.3 \text{ V}$

Short Circuit SOA Capability
Square RBSOA

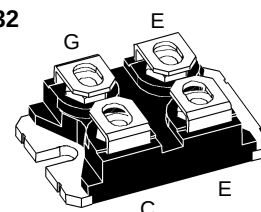


IXDN 55N120



IXDN 55N120 D1

miniBLOC, SOT-227 B
E153432



E = Emitter ①, C = Collector
G = Gate, E = Emitter ①

① Either Emitter terminal can be used as Main or Kelvin Emitter

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 20 \text{ k}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	100	A
I_{C90}	$T_C = 90^\circ\text{C}$	62	A
I_{CM}	$T_C = 90^\circ\text{C}$, $t_p = 1 \text{ ms}$	124	A
RBSOA	$V_{GE} = \pm 15 \text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 22 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 100$ $V_{CEK} < V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = \pm 15 \text{ V}$, $V_{CE} = V_{CES}$, $T_J = 125^\circ\text{C}$ $R_G = 22 \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	IGBT Diode	450 220 W W
V_{ISOL}	50/60 Hz; $I_{ISOL} \leq 1 \text{ mA}$	2500	V~
T_J		-40 ... +150	$^\circ\text{C}$
T_{stg}		-40 ... +150	$^\circ\text{C}$
M_d	Mounting torque Terminal connection torque (M4)	1.5/13 1.5/13	Nm/lb.in. Nm/lb.in.
Weight		30	g

Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- optional ultra fast diode
- International standard package miniBLOC

Advantages

- Space savings
- Easy to mount with 2 screws
- High power density

Typical Applications

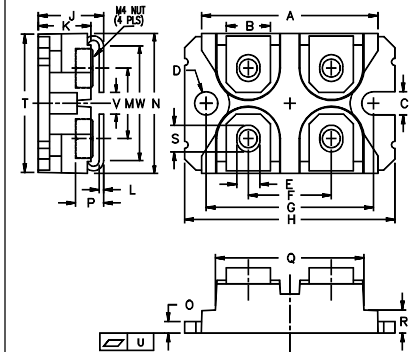
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 2 \text{ mA}$, $V_{CE} = V_{GE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		6	3.8 mA mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 500 \text{ nA}$
$V_{CE(sat)}$	$I_C = 55 \text{ A}$, $V_{GE} = 15 \text{ V}$		2.3	2.8 V

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		3300	pF
C_{oes}			500	pF
C_{res}			220	pF
Q_g	$I_C = 50\text{ A}, V_{GE} = 15\text{ V}, V_{CE} = 0.5\text{ V}_{CES}$		240	nC
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 55\text{ A}, V_{GE} = \pm 15\text{ V},$ $V_{CE} = 600\text{ V}, R_G = 22\ \Omega$		100	ns
t_r			70	ns
$t_{d(off)}$			500	ns
t_f			70	ns
E_{on}			8.4	mJ
E_{off}			6.2	mJ
R_{thJC}	Package with heatsink compound			0.28 K/W
R_{thCK}			0.1	K/W

Reverse Diode (FRED) [D1 version only]

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = 55\text{ A}, V_{GE} = 0\text{ V}$	2.4	2.6	V
	$I_F = 55\text{ A}, V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$	1.9		V
I_F	$T_C = 25^\circ\text{C}$		110	A
	$T_C = 90^\circ\text{C}$		60	A
I_{RM}	$I_F = 55\text{ A}, -di_F/dt = 400\text{ A}/\mu\text{s}, V_R = 600\text{ V}$	40		A
t_{rr}	$V_{GE} = 0\text{ V}, T_J = 125^\circ\text{C}$	200		ns
t_{rr}	$I_F = 1\text{ A}, -di_F/dt = 100\text{ A}/\mu\text{s}, V_R = 30\text{ V}, V_{GE} = 0\text{ V}$	40		ns
R_{thJC}			0.6	K/W

miniBLOC, SOT-227 B


M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.20	1.489	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004
V	3.30	4.57	0.130	0.180
W	0.780	0.830	0.031	0.033

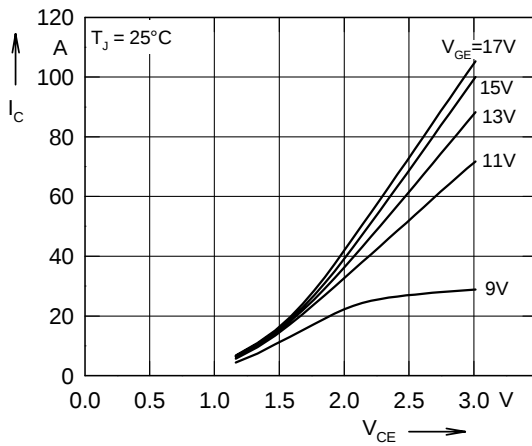


Fig. 1 Typ. output characteristics

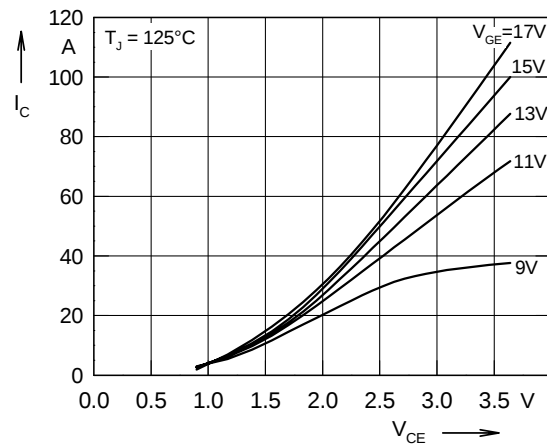


Fig. 2 Typ. output characteristics

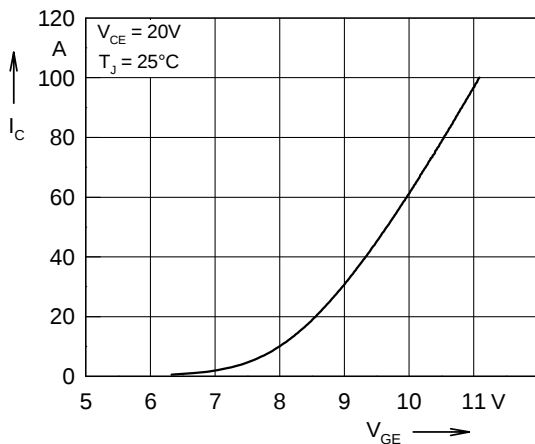


Fig. 3 Typ. transfer characteristics

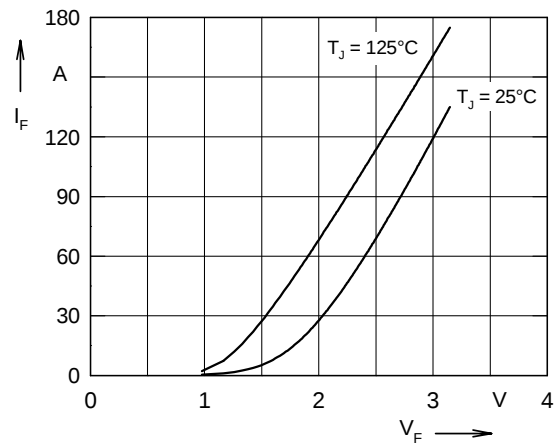


Fig. 4 Typ. forward characteristics of free wheeling diode

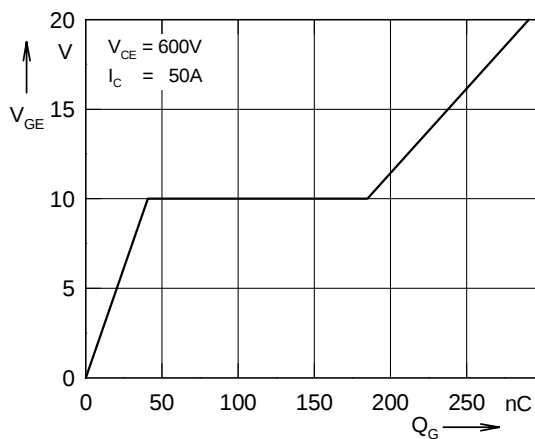


Fig. 5 Typ. turn on gate charge

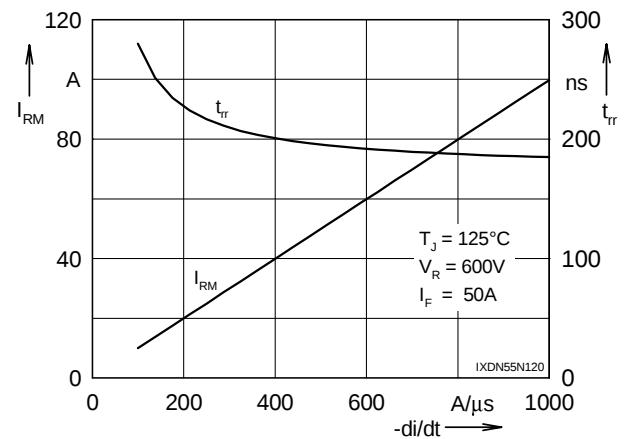


Fig. 6 Typ. turn off characteristics of free wheeling diode

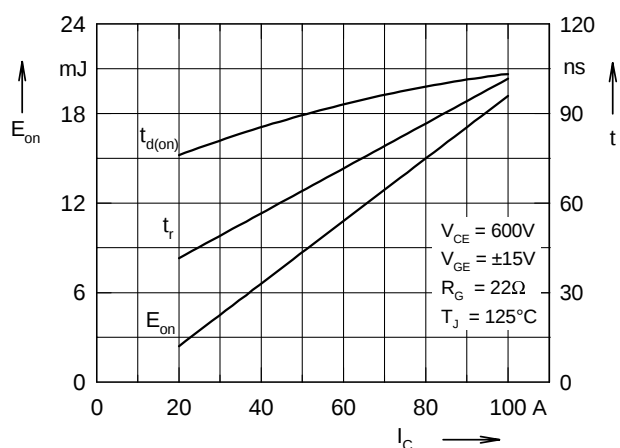


Fig. 7 Typ. turn on energy and switching times versus collector current

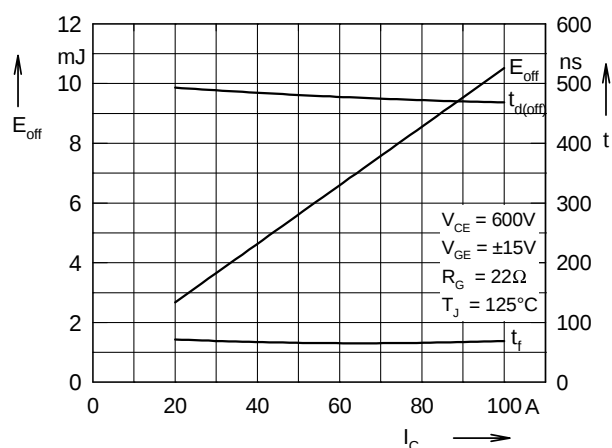


Fig. 8 Typ. turn off energy and switching times versus collector current

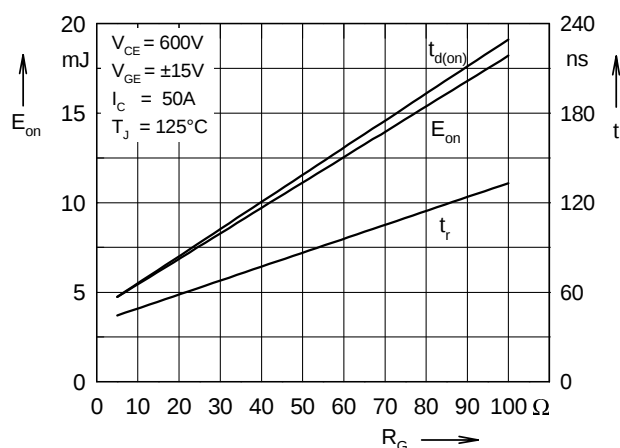


Fig. 9 Typ. turn on energy and switching times versus gate resistor

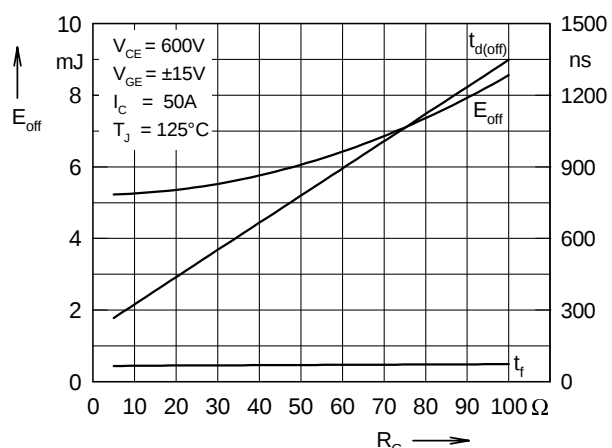


Fig. 10 Typ. turn off energy and switching times versus gate resistor

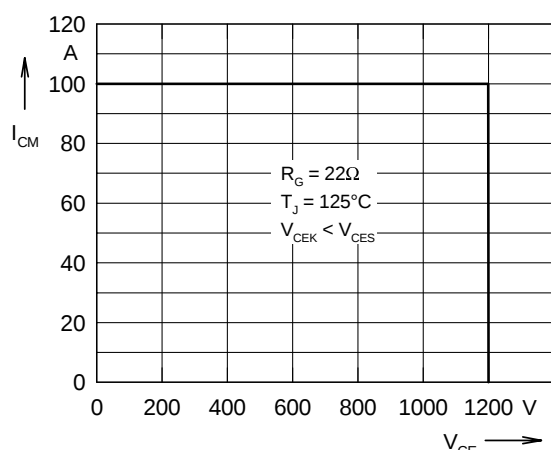


Fig. 11 Reverse biased safe operating area RBSOA

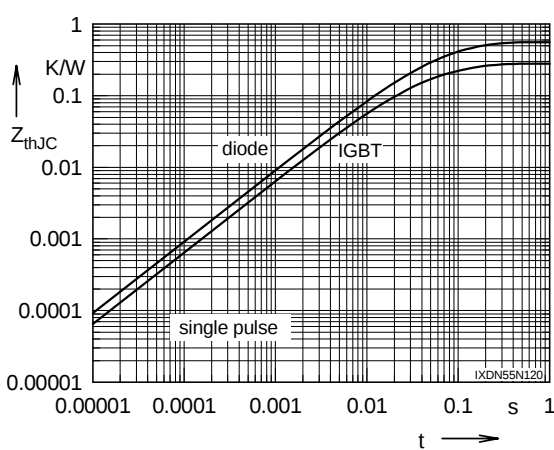


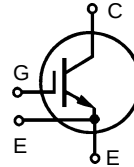
Fig. 12 Typ. transient thermal impedance

High Voltage IGBT

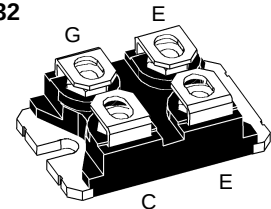
IXDN 75N120

$$\begin{aligned} V_{CES} &= 1200 \text{ V} \\ I_{C25} &= 150 \text{ A} \\ V_{CE(sat) \text{ typ}} &= 2.2 \text{ V} \end{aligned}$$

Short Circuit SOA Capability
Square RBSOA



miniBLOC, SOT-227 B
E153432



Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 20 \text{ k}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	150	A
I_{C90}	$T_C = 90^\circ\text{C}$	95	A
I_{CM}	$T_C = 90^\circ\text{C}$, $t_p = 1 \text{ ms}$	190	A
RBSOA	$V_{GE} = \pm 15 \text{ V}$, $T_J = 125^\circ\text{C}$, $R_G = 15 \Omega$ Clamped inductive load, $L = 30 \mu\text{H}$	$I_{CM} = 150$ $V_{CEK} < V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = \pm 15 \text{ V}$, $V_{CE} = V_{CES}$, $T_J = 125^\circ\text{C}$ $R_G = 15 \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$ IGBT	660	W
V_{ISOL}	50/60 Hz; $I_{ISOL} \leq 1 \text{ mA}$	2500	V~
T_J		-40 ... +150	$^\circ\text{C}$
T_{stg}		-40 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.5/13	Nm/lb.in.
	Terminal connection torque (M4)	1.5/13	Nm/lb.in.
Weight		30	g

E = Emitter ①, C = Collector
G = Gate, E = Emitter ①

① Either Emitter terminal can be used as Main or Kelvin Emitter

Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- International standard package miniBLOC

Advantages

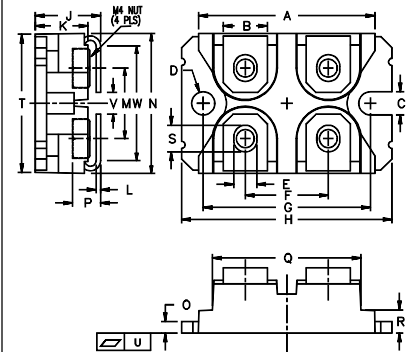
- Space savings
- Easy to mount with 2 screws
- High power density

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 3 \text{ mA}$, $V_{CE} = V_{GE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		6	4 mA mA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 500 \text{ nA}$
$V_{CE(sat)}$	$I_C = 75 \text{ A}$, $V_{GE} = 15 \text{ V}$	2.2	2.7	V

Typical Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		5500	pF
C_{oes}			750	pF
C_{res}			330	pF
Q_g	$I_C = 75\text{ A}, V_{GE} = 15\text{ V}, V_{CE} = 0.5\text{ V}_{CES}$		360	nC
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 75\text{ A}, V_{GE} = \pm 15\text{ V},$ $V_{CE} = 600\text{ V}, R_G = 15\ \Omega$		100	ns
t_r			50	ns
$t_{d(off)}$			650	ns
t_f			50	ns
E_{on}			12.1	mJ
E_{off}			10.5	mJ
R_{thJC}	Package with heatsink compound			0.19 K/W
R_{thCK}			0.1	K/W

miniBLOC, SOT-227 B


M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.20	1.489	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004
V	3.30	4.57	0.130	0.180
W	0.780	0.830	0.031	0.033

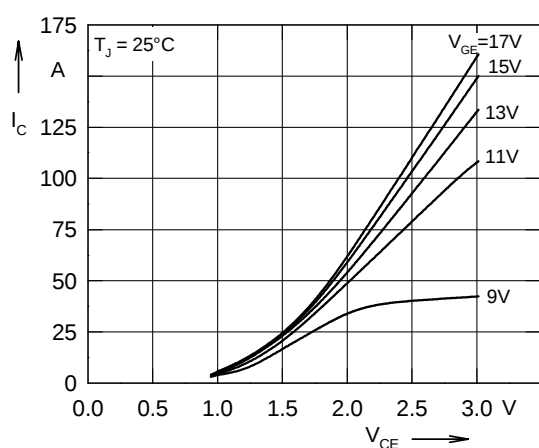


Fig. 1 Typ. output characteristics

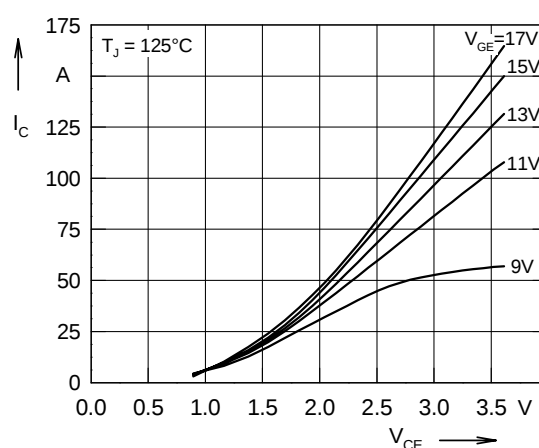


Fig. 2 Typ. output characteristics

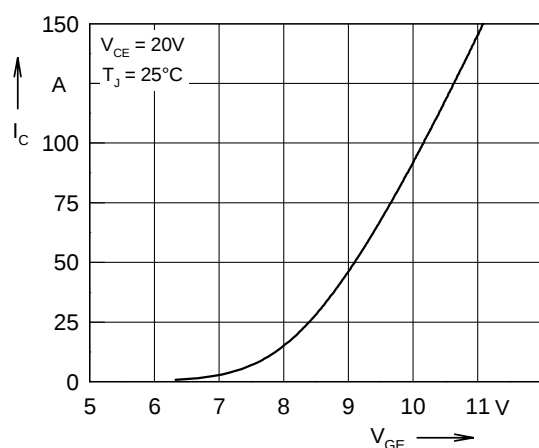


Fig. 3 Typ. transfer characteristics

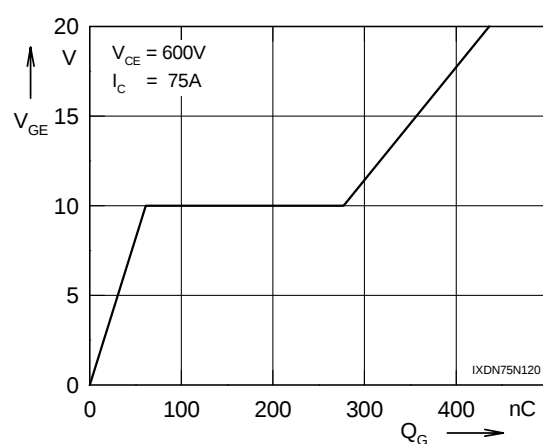


Fig. 4 Typ. turn on gate charge

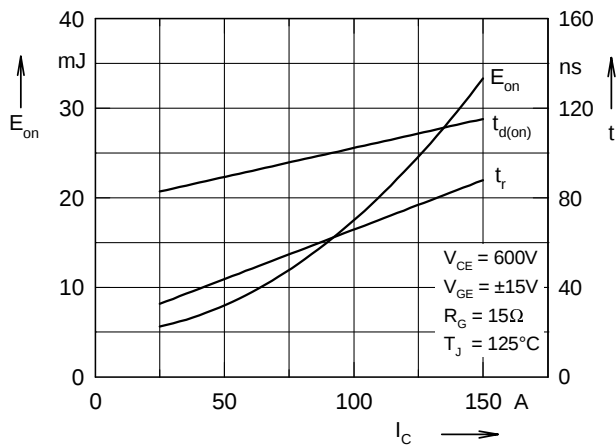


Fig. 5 Typ. turn on energy and switching times versus collector current

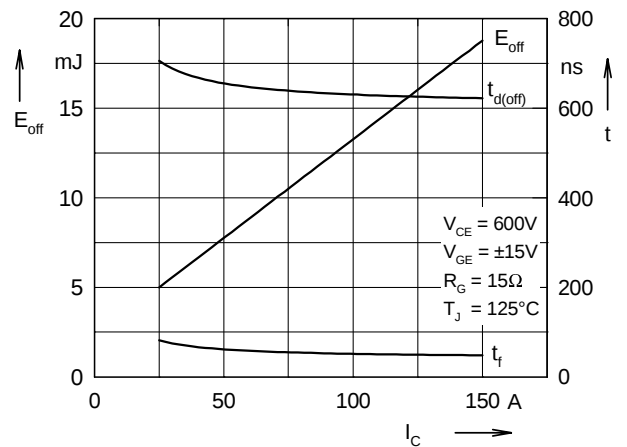


Fig. 6 Typ. turn off energy and switching times versus collector current

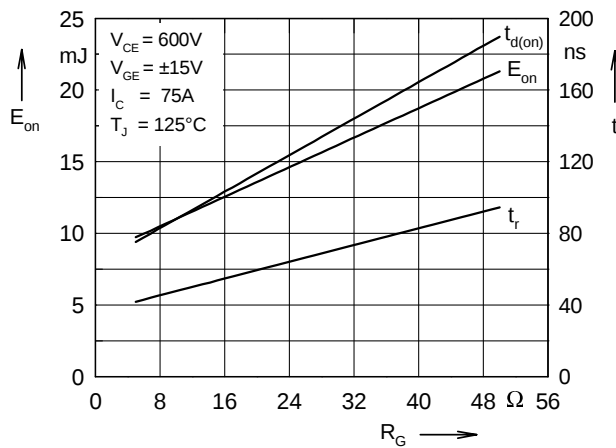


Fig. 7 Typ. turn on energy and switching times versus gate resistor

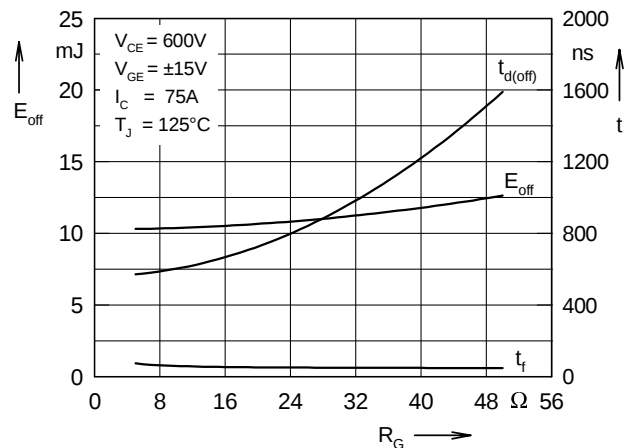


Fig. 8 Typ. turn off energy and switching times versus gate resistor

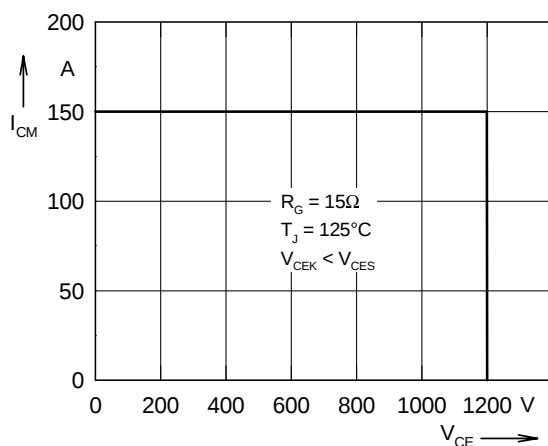


Fig. 9 Reverse biased safe operating area RBSOA

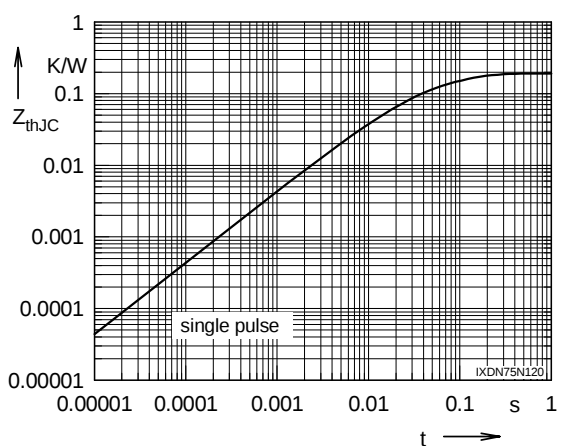


Fig. 10 Typ. transient thermal impedance

